

**ROCHESTER INSTITUTE OF TECHNOLOGY
MICROELECTRONIC ENGINEERING**

Bruce Furnace Recipes

Dr. Lynn Fuller

Webpage: <http://people.rit.edu/lffee>

Electrical and Microelectronic Engineering

Rochester Institute of Technology

82 Lomb Memorial Drive

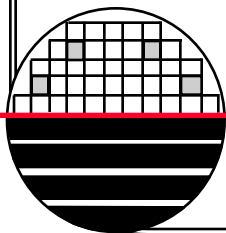
Rochester, NY 14623-5604

Tel (585) 475-2035

Fax (585) 475-5041

Email: Lynn.Fuller@rit.edu

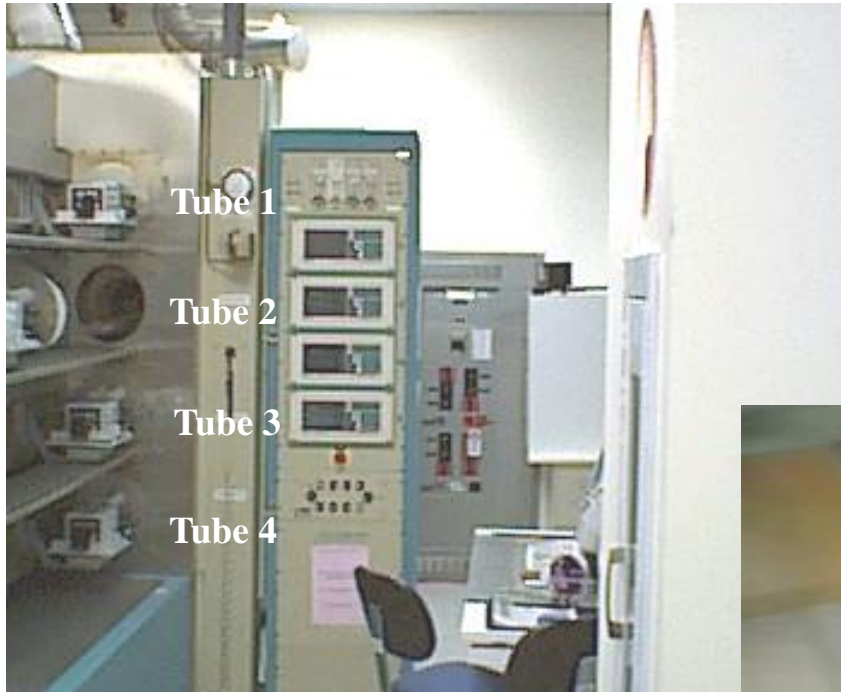
Department Webpage: <http://www.microe.rit.edu>



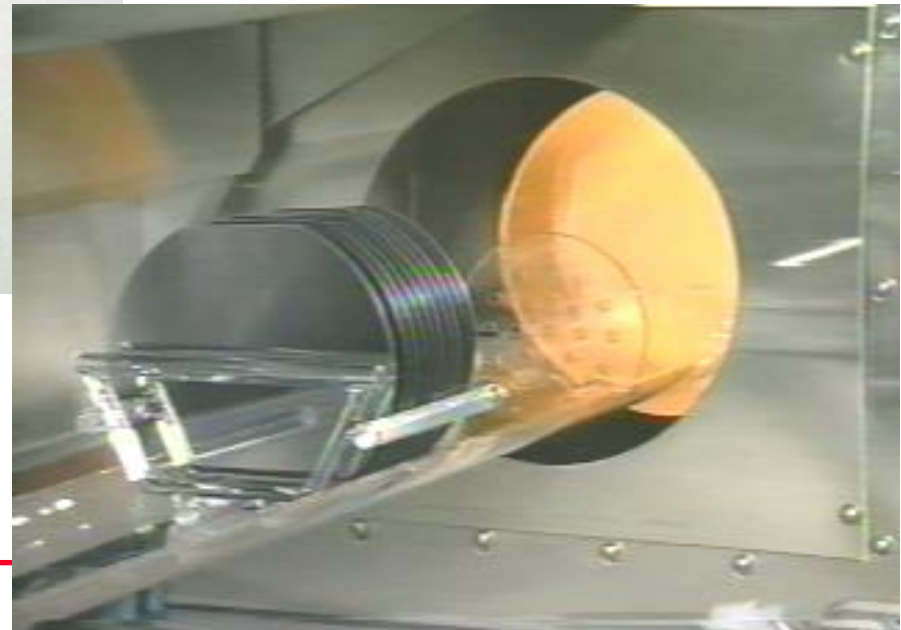
OUTLINE

Bruce Furnace
Bruce Furnace Recipes
Advanced Recipes
Calculations
List of Recipes
Recipe Details
Measurement of Oxide Thickness
Recall of Run Data
Stabilization After Push
Non Uniform Oxide Growth Problems
SPC
Out of Control Action Plans
Bake of Spin-on Dopants
Creating New Recipes
References

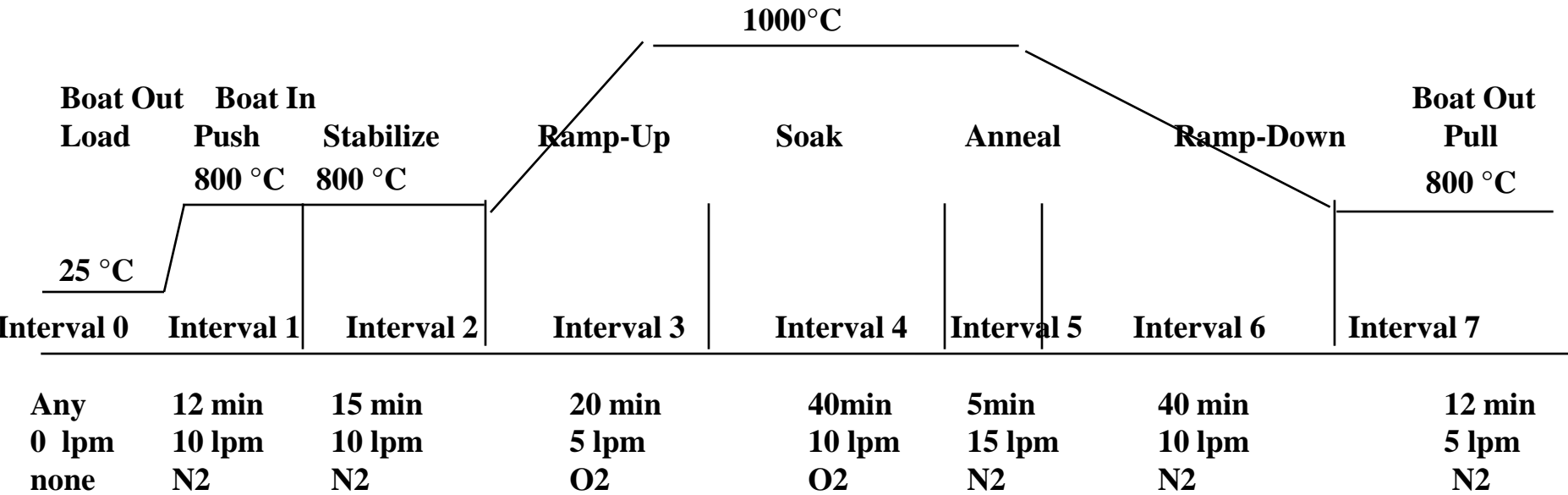
BRUCE FURNACE



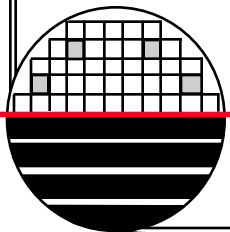
Tube 1 Steam Oxides
Tube 2 P-type Diffusion
Tube 3 N-type Diffusion
Tube 4 Dry Oxides and
Gate Oxides



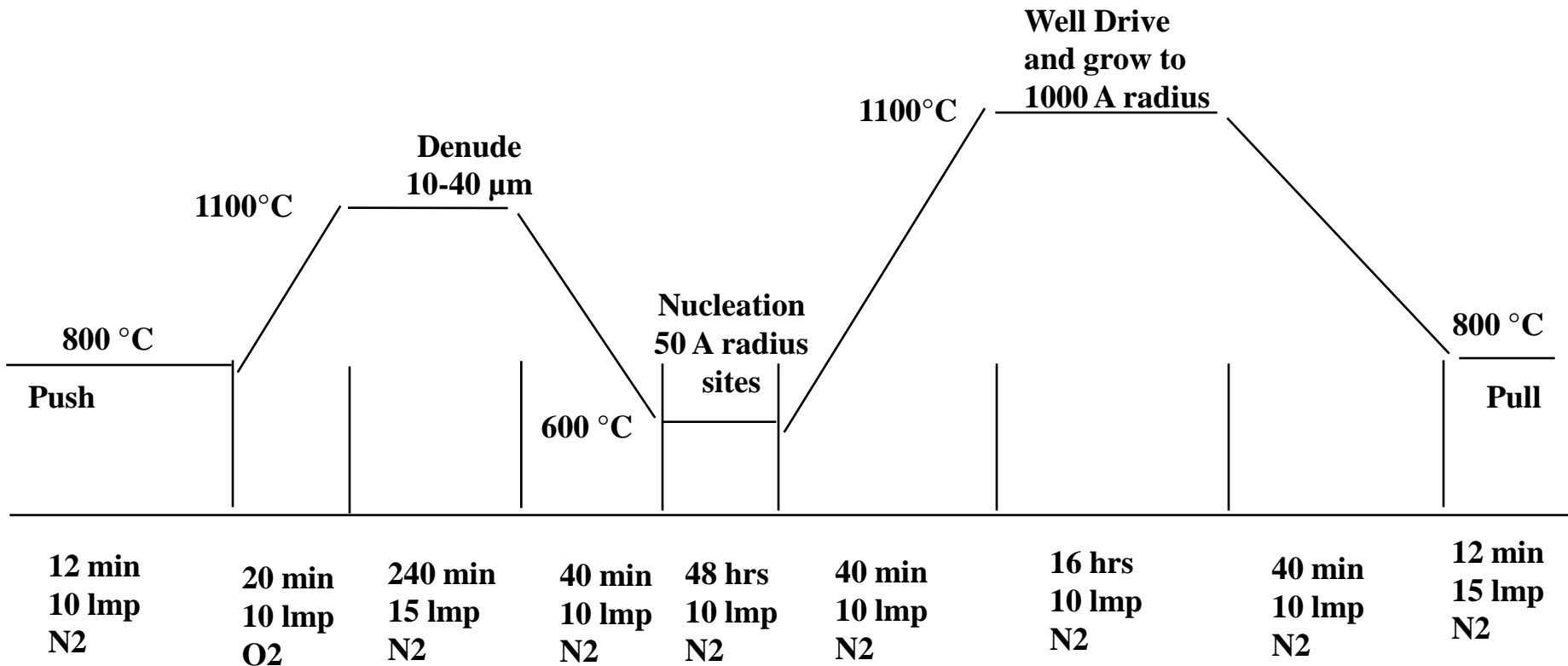
BRUCE FURNACE RECIPES



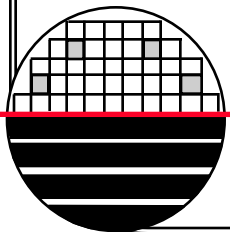
At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.



ADVANCED FURNACE RECIPES

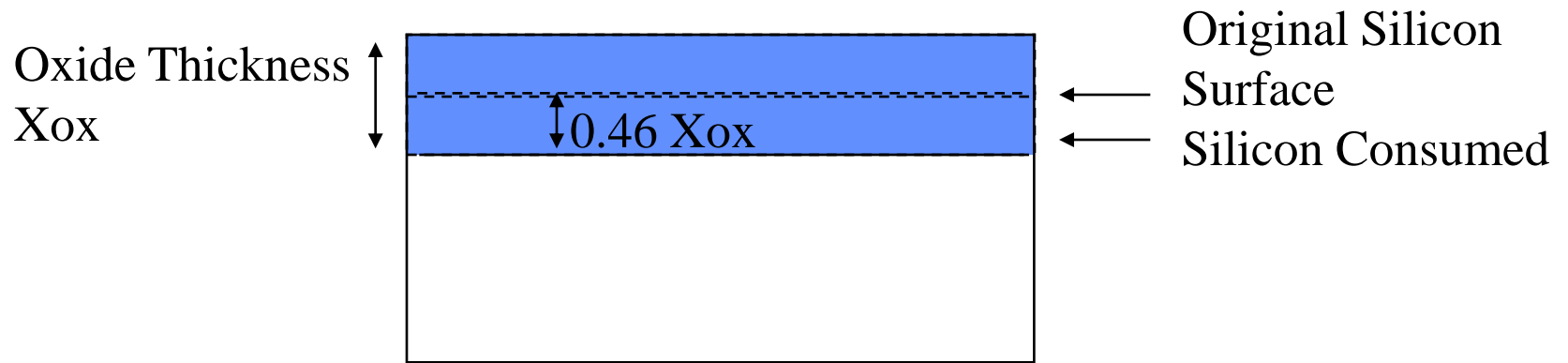


15-20 ppma Oxygen Starting Wafers



Rochester Institute of Technology
Microelectronic Engineering

OXIDE GROWTH



Dry oxide O₂ only

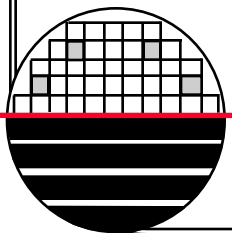
Wet oxide O₂ bubbled through water

Steam burn H₂ in O₂ to make H₂O (steam)

USING EXCEL SPREADSHEET FOR OXIDE GROWTH CALCULATIONS

	A	B	C	D	E	F	G	H	I	J
1	ROCHESTER INSTITUTE OF TECHNOLOGY						OXIDE.XLS			
2	MICROELECTRONIC ENGINEERING						7/4/2014			
3										
4	CALCULATION OF OXIDE THICKNESS						Dr. Lynn Fuller / Jamie Wasiewicz			
5										
6	To use this spreadsheet change the values in the white boxes. The rest of the sheet is									
7	protected and should not be changed unless you are sure of the consequences. The									
8	calculated results are shown in the purple boxes. O2 bubbled through warm water is "wet",									
9	burning H2 with O2 is called "steam"									
10										
11	CONSTANTS			VARIABLES			CHOICES			
12	K	1.38E-23 J/K		Temp =		<input type="text" value="900"/>	°C	wet	<input type="checkbox"/>	
13	(Bo/Ao) dry	6230000 μm/hr		time =		<input type="text" value="42"/>	min	dry	<input type="checkbox"/>	
14	Ea (dry)	2 eV		Partial Pressure, p =		<input type="text" value="1.00"/>	Atm	steam	<input type="checkbox"/>	
15	(Bo/Ao) wet	89500000 μm/hr						<100>	<input type="checkbox"/>	
16	Ea (wet)	2.05 eV						<111>	<input type="checkbox"/>	
17	(Bo/Ao) steam	1.63E+08 μm/hr		Xint =		<input type="text" value="0"/>	Å			
18	Ea (steam)	2.05 eV								
19	Bo dry	7.72E+02 μm ² /hr								
20	Ea (dry)	1.23 eV								
21	Bo wet	2.14E+02 μm ² /hr		Silicon VLSI Technology, Plummer, Deal, Griffin						
22	Ea (wet)	0.71 eV		Prentice Hall, 2000, pg 319-369						
23	Bo steam	3.86E+02 μm ² /hr								
24	Ea (steam)	0.78 eV		(Bo/Ao)/1.68 for <100>						
25										
26	CALCULATIONS:									
27										
28	Xox (Oxide thickness)=(A/2){[1+(t+Tau)4B/A^2]^0.5 -1} =						<input type="text" value="1005"/>			
29										
30	B = [Bo exp (-Ea/KTemp)]*p				<input type="text" value="0.1737431"/>		μm ² /hr			
31	B/A = [(Bo/Ao) exp (-Ea/KTemp)]*p				<input type="text" value="1.57E-01"/>		μm/hr			
32	A				<input type="text" value="1.1100164"/>		μm			
33	Tau = (Xi2+A.Xi)/B				<input type="text" value="0"/>		hr			
34										
35										
36	Xox	↑ ↓		Oxide-SiO2		←		Original Silicon Surface Prior to Oxide Growth		
37			Silicon		↑		0.46 Xox (silicon consumed)			
38										
39										
40										
41										
42										

These spreadsheets are available on Dr. Fullers webpage.



USING EXCEL SPREADSHEET FOR D/S JUNCTION DEPTH & SHEET RHO CALCULATIONS

CALCULATION OF ION IMPLANT JUNCTION DEPTH AND SHEET RESISTANCE AFTER DRIVE-IN

CONSTANTS

	Boron	Phosorous	VALUE	UNITS
Max Mobility of n-type carriers	470.5	1414	q = 1.60E-19	Coul
Min Mobility of p-type carriers	44.9	68.5		
Nref	2.23E+17	9.20E+16		
alpha	0.719	0.711		

GIVEN

	VALUE	UNITS
Starting Wafer Resistivity	10	ohm-cm
Starting Wafer Type	0	1 or 0
	1	1 or 0

Pre Deposition Ion Implant Dose = 9.50E+12 ions/cm2

Implant Beam Current = 20 μA

Implant Time for 6" wafers = 0.24 min

Drive-in Temperature = 1100 °C
 Drive-in Time = 750 min

CALCULATE

	VALUE	UNITS
Diffusion Constant at Temperature of Drive-in	1.33E-13	cm2/sec
Diffusion Constant x time (use to adjust t for multiple Drive-ins)	5.99E-09	cm2

CALCULATION OF DIFFUSION CONSTANTS

	D0 (cm2/s)	EA (eV)
Boron	0.76	3.46
Phosphorous	3.85	3.66

CALCULATIONS

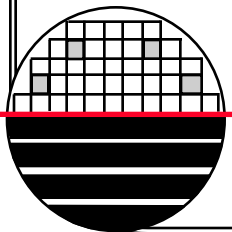
Substrate Doping = $1 / (q \mu_{max} Rho)$ Nsub = 1.33E+15 cm-3

RESULTS

	VALUE	UNITS
Pre deposition Dose	9.50E+12	atoms/cm2
xj after drive-in = $((4 Dd td/QA) \ln (Nsub (\pi Ddtd)^{0.5}))^{0.5}$	3.08	μm
average doping Nave = Dose/xj	3.09E+16	atoms/cm3
mobility (μ) at Doping equal to Nave	990	cm2/V-s
Sheet Resistance = $1/(q (\mu(Nave))Dose)$	664.5	ohms
Surface Concentration = $Dose / (pDt)^{0.5}$	6.93E+16	cm-3

Diffusion Constants (cm2/sec) Solid Solubility (cm-3)

These spreadsheets are available on Dr. Fullers webpage.

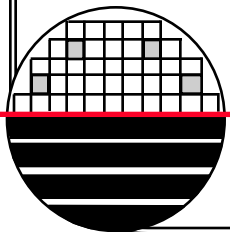
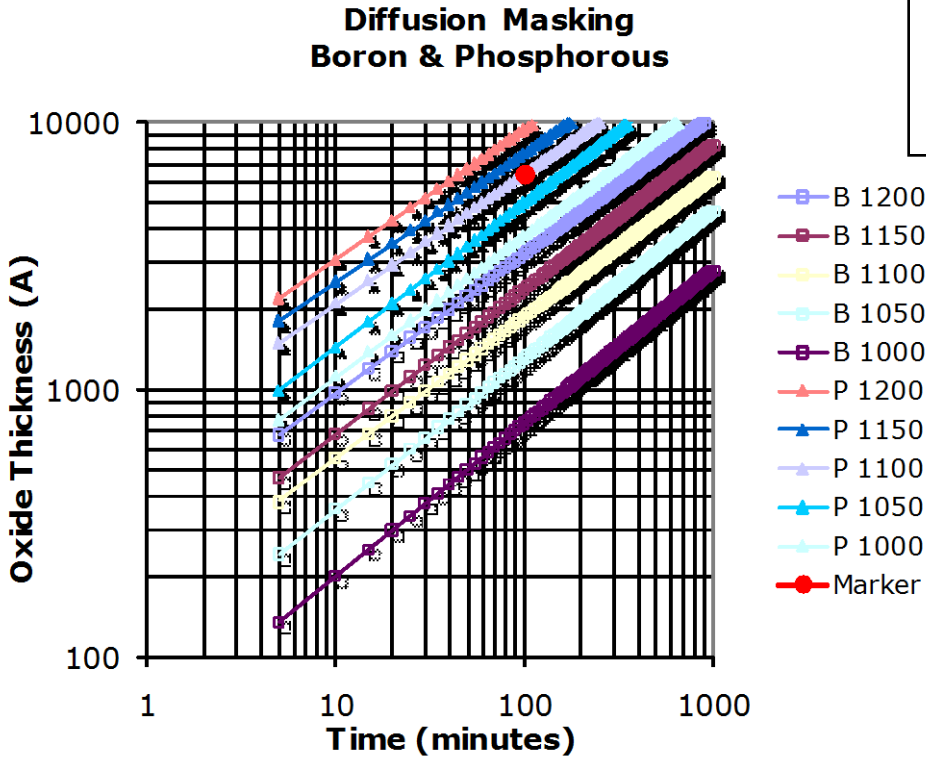


MINIMUM OXIDE NEEDED TO MASK DIFFUSION

or result will be in error.

Dopant		Diffusion		
Boron	<input type="text" value="0"/>	Temp.	<input type="text" value="1100"/> °C	
Phosphorous	<input type="text" value="1"/>	Time	<input type="text" value="100"/> minutes	
Oxide		Boron	1867 Angstroms	
Fitted to data taken from Hamilton and Howard		Phosp	6399 Angstroms	
			<input type="text" value="6399"/> Angstroms	

These spreadsheets are available on Dr. Fullers webpage.



OXIDE THICKNESS COLOR CHART

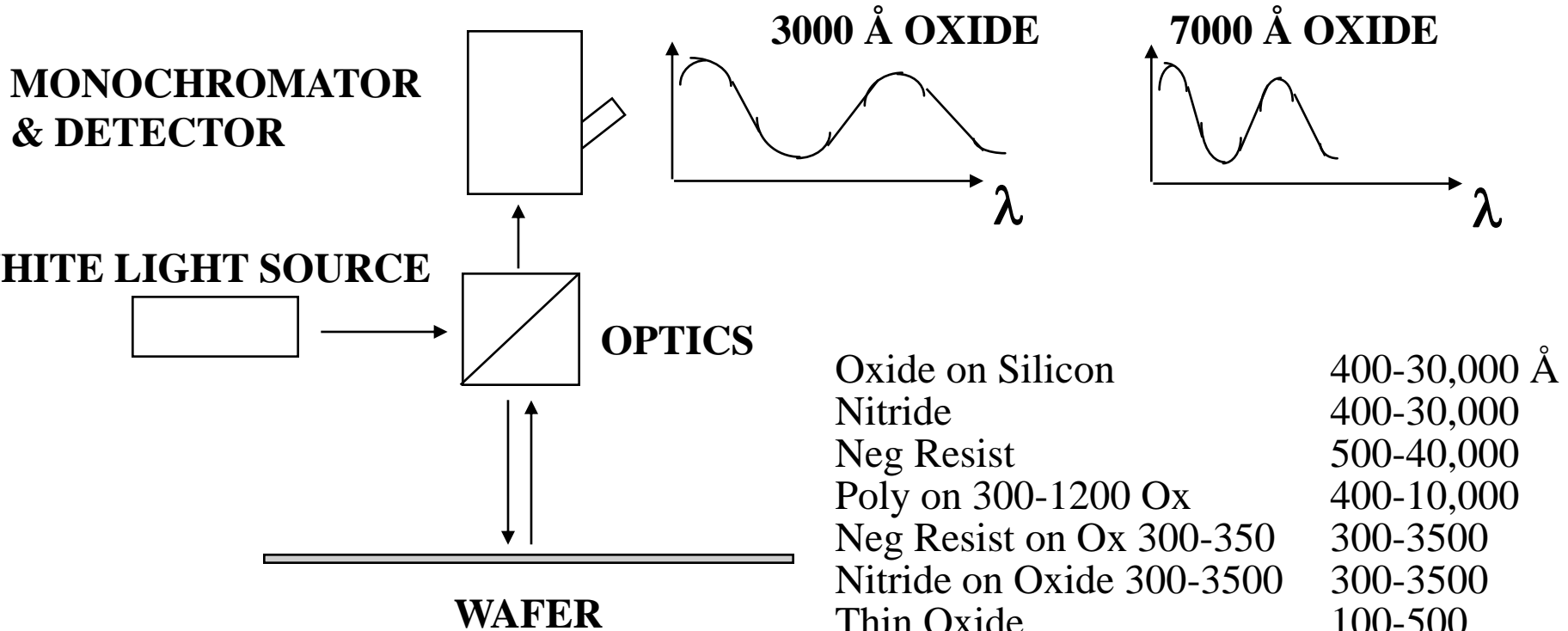
Thickness	Color
500	Tan
700	Brown
1000	Dark Violet - Red Violet
1200	Royal Blue Blue
1500	Light Blue - Metallic Blue
1700	Metallic - very light Yellow Green
2000	Light Gold or Yellow - Slightly Metallic
2200	Gold with slight Yellow Orange
2500	Orange - Melon
2700	Red Violet
3000	Blue - Violet Blue
3100	Blue Blue
3200	Blue - Blue Green
3400	Light Green
3500	Green - Yellow Green
3600	Yellow Green
3700	Yellow
3900	Light Orange
4100	Carnation Pink
4200	Violet Red
4400	Red Violet
4600	Violet
4700	Blue Violet

Thickness	Color
4900	Blue Blue
5000	Blue Green
5200	Green
5400	Yellow Green
5600	GreenYellow
5700	Yellow - "Yellowish"(at times appears to be Lt gray or matel
5800	Light Orange or Yellow - Pink
6000	Carnation Pink
6300	Violet Red
6800	"Bluish"(appears violet red, Blue Green, looks Blue
7200	Blue Green - Green
7700	"Yellowish"
8000	Orange
8200	Salmon
8500	Dull, Lght Red Violet
8600	Violet
8700	Blue Violet
8900	Blue Blue
9200	Blue Green
9500	Dull Yellow Green
9700	Yellow - "Yellowish"
9900	Orange
10000	Carnation Pink

Nitride Thickness = (Oxide Thickness)(Oxide Index/Nitride Index)
 Eg. Yellow Nitride Thickness = (2000)(1.46/2.00) = 1460

REFLECTANCE SPECTROMETER (NANOSPEC - THICKNESS MEASUREMENT)

INCIDENT WHITE LIGHT, THE INTENSITY OF THE REFLECTED LIGHT IS MEASURED VS WAVELENGTH



Oxide on Silicon	400-30,000 Å
Nitride	400-30,000
Neg Resist	500-40,000
Poly on 300-1200 Ox	400-10,000
Neg Resist on Ox 300-350	300-3500
Nitride on Oxide 300-3500	300-3500
Thin Oxide	100-500
Thin Nitride	100-500
Polyimide	500-10,000
Positive Resist	500-40,000
Pos Resist on Ox 500-15,000	4,000-30,000

NANOSPEC FILM THICKNESS MEASUREMENT TOOL



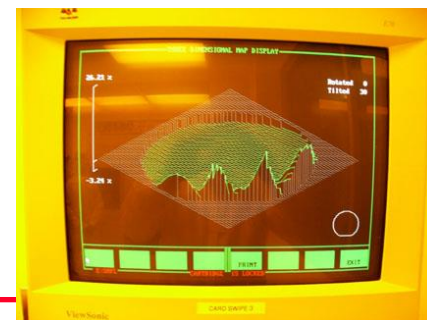
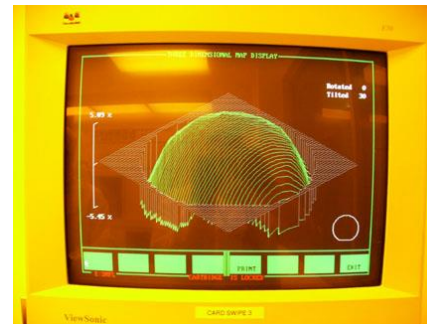
Record:

Color = Blue-Green

Color Chart Thickness = \AA

Nanospec Thickness = \AA

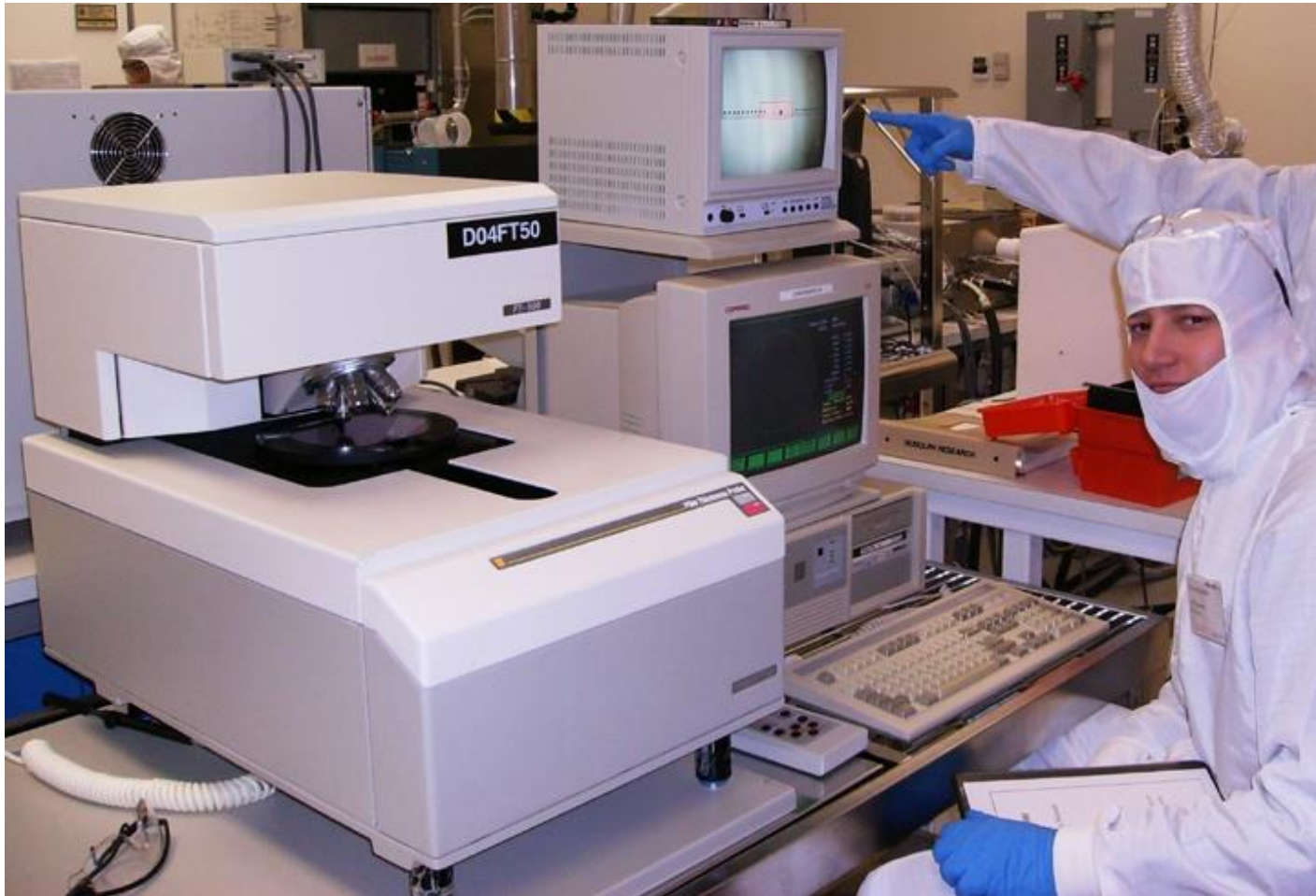
TENCORE FT-300 SPECROMAP



Record:

- Mean
- Std Deviation
- Min
- Max
- No of Points

FT500



*Rochester Institute of Technology
Microelectronic Engineering*

ELLIPSOMETER MEASUREMENTS

Measure wafers C1 and C2



Pattern 20 is 1 point in center of wafer
Pattern 22 is 5 points on 4" wafer
Pattern 25 is 5 points on 6" wafer

Recipe 03 is oxide on silicon
Recipe 07 is nitride on oxide on silicon
Recipe 02 is used for one film and finds
thickness and index of refraction

MEASURE C1 AND C2 ON SCA-2500

Login: FACTORY

Password: OPER

<F1> Operate

<F1> Test Center the wafer on the stage

**Select (use arrow keys on the numeric pad (far right on the keyboard)
space bar, page up, etc)**

PROGRAM = FAC-P or FAC-N

LOT ID = F040909

WAFER NO. = D1

TOX = 463 (from nanospec)

<F12> start test and wait for measurement

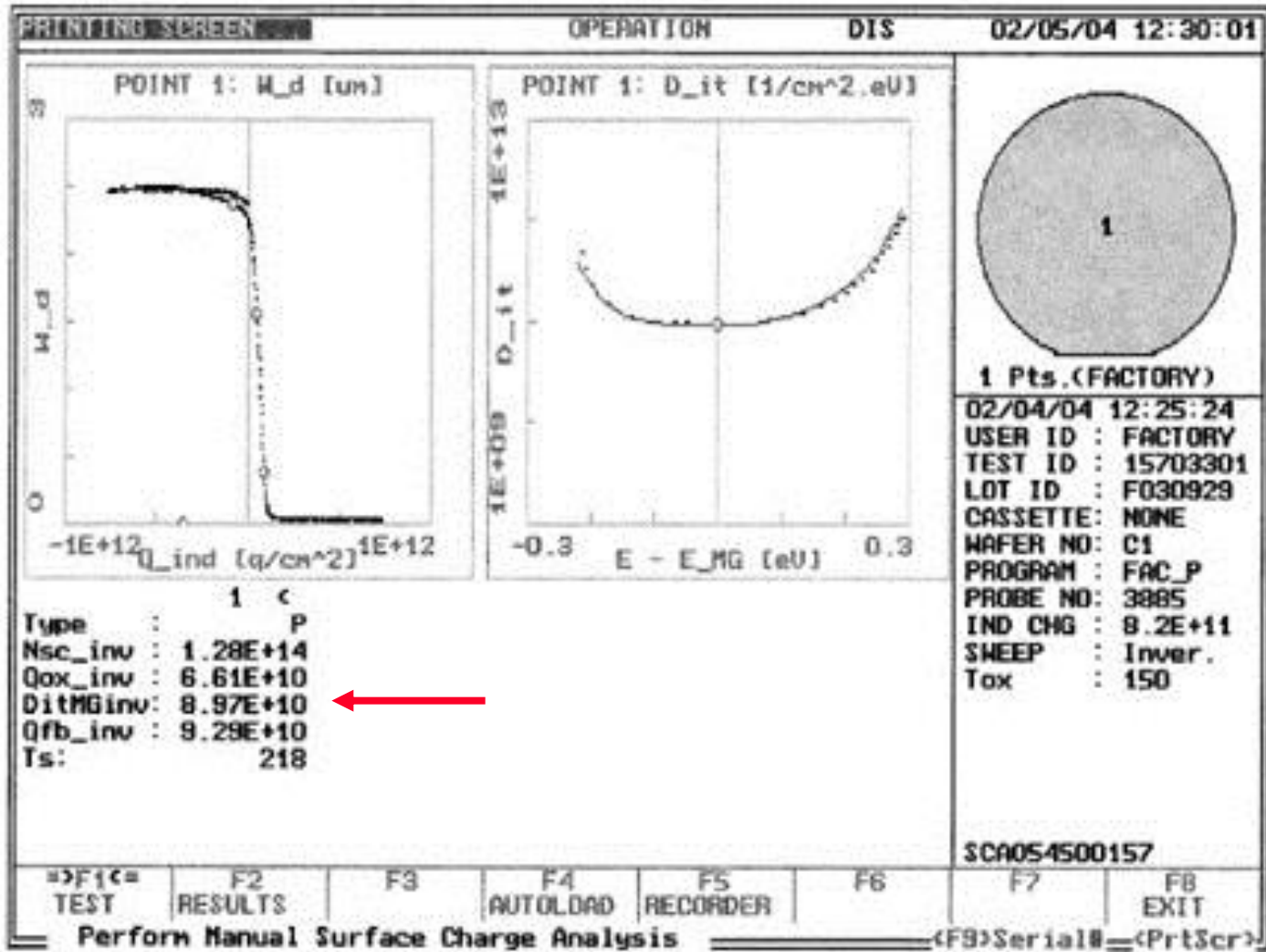
<Print Screen> print results

<F8> exit and log off

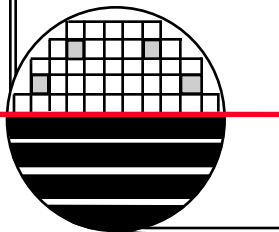
**<ESC> can be used anytime, but wait for
current test to be completed**

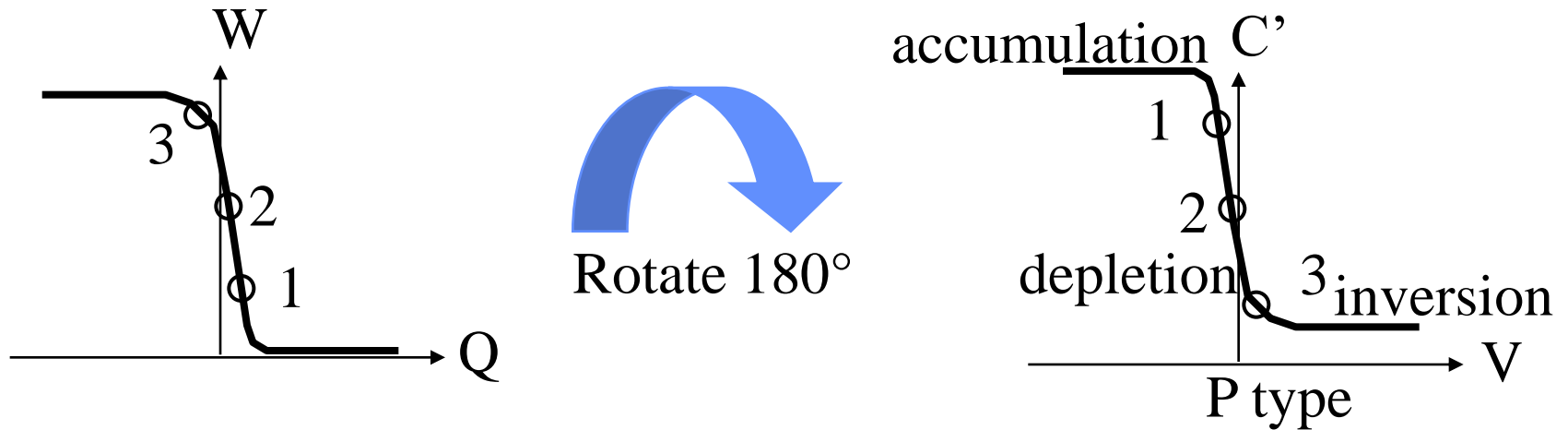


SCA MEASUREMENT OF GATE OXIDE



PLAY



SCA THEORY

Point 1 is at flat band bias, Q_{fb} is extracted

Point 2 is at intrinsic bias, Q_{ox} is extracted, if Q_{ox} is not equal to Q_{FB} then there are interface traps, D_{it} is calculated from slope of region between point 1 and 3.

Point 3 is at onset of inversion where N_{sc} is extracted

Lifetime, T_s , is measured in inversion

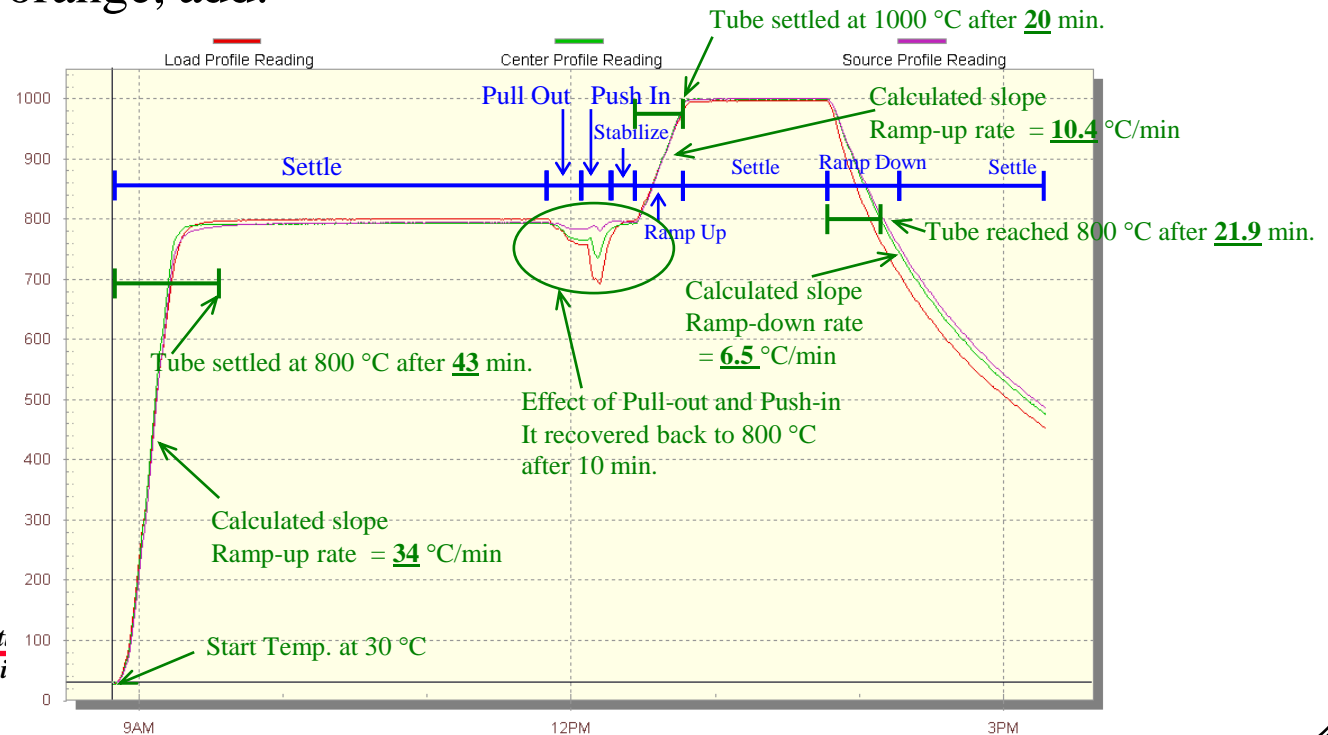
P or N type is determined from shape of the curve

$$Q = C'V$$

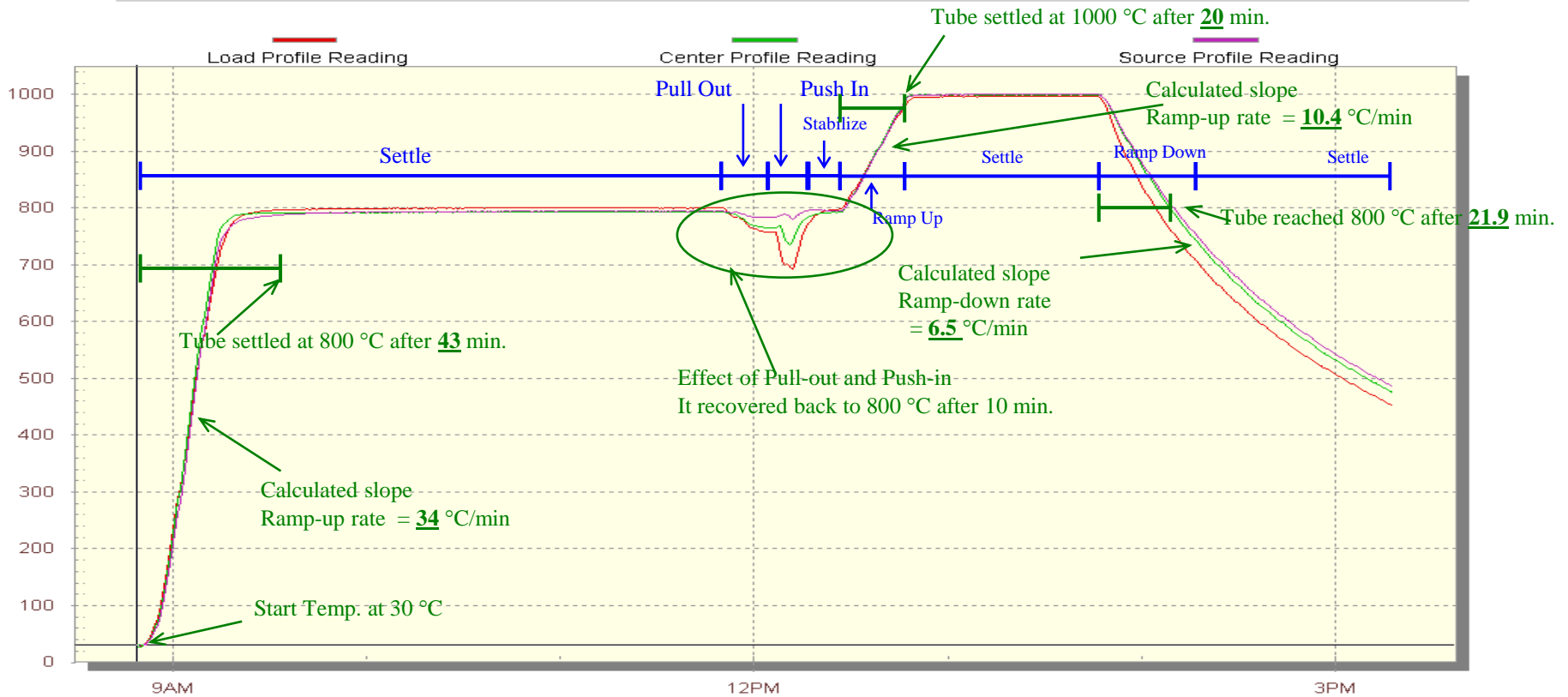
$$C' = \epsilon_0 \epsilon_r / W$$

RECALL RUN DATA

Click on the furnace tube of interest.
Click on the graph icon on the left end of the top banner.
Select last month.
Select the furnace run of interest.
Select the items to be graphed. Example: center profile, red, add;
nitrogen flow, blue, add; oxygen flow, green, add;
hydrogen flow, orange, add.



STABILIZE AFTER PUSH



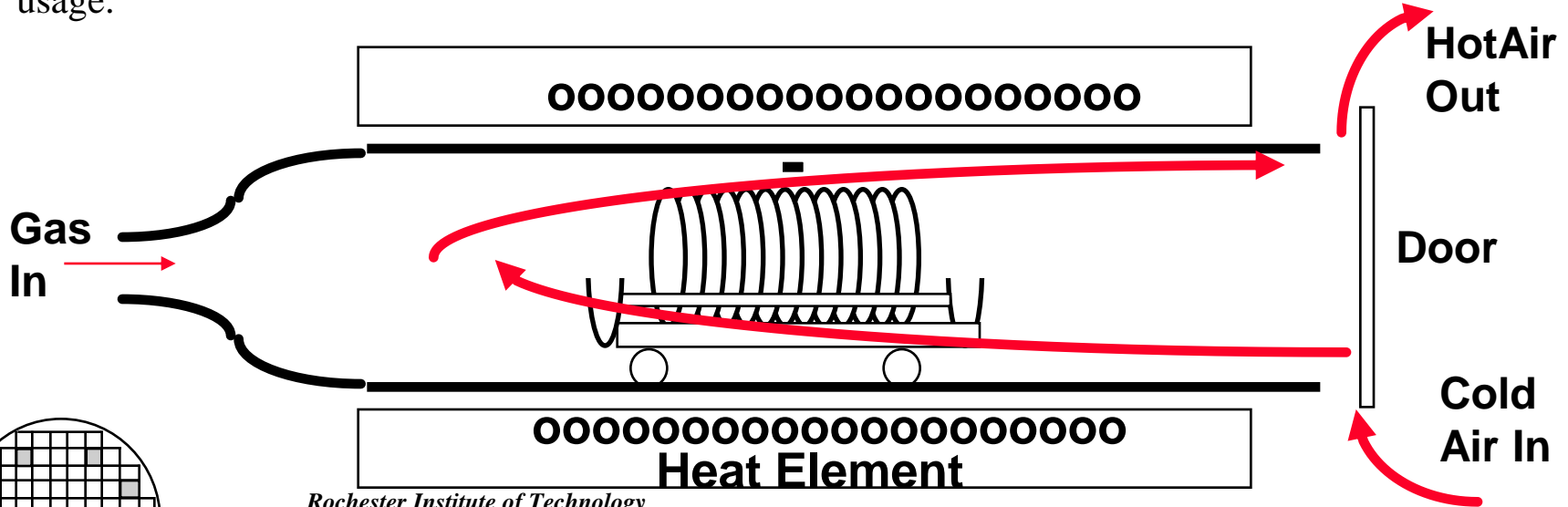
Because of the temperature drop during pull/out and load and the push/in we need to add a stabilize step at 800C in nitrogen prior to ramp up. Include a 15 min stabilize after push/in to all recipes.

NON UNIFORM OXIDE GROWTH PROBLEMS

Non uniform oxide growth (top different from bottom) is often caused by not having the door closed all the way against the tube allowing room air to mix with the gas in the furnace. A similar effect is caused by having the gas flow rates too high or too low. The flow should slowly push a volume of air down the tube, without turbulence and without high velocity as it passes by the wafers. If the flow is too low then the door needs to be closed more accurately.

Use Total flow (lpm) = v (cm/s) x Area (cm²) x 60 (s/m) x 0.001 (l/cm³)
and let $v = 1.0$ cm/s. For 20 cm diameter tube Total Flow= 18 lpm

The Bruce Furnace at RIT uses flows from 5 lpm to 15 lpm, These are all on the low side to reduce gas usage.

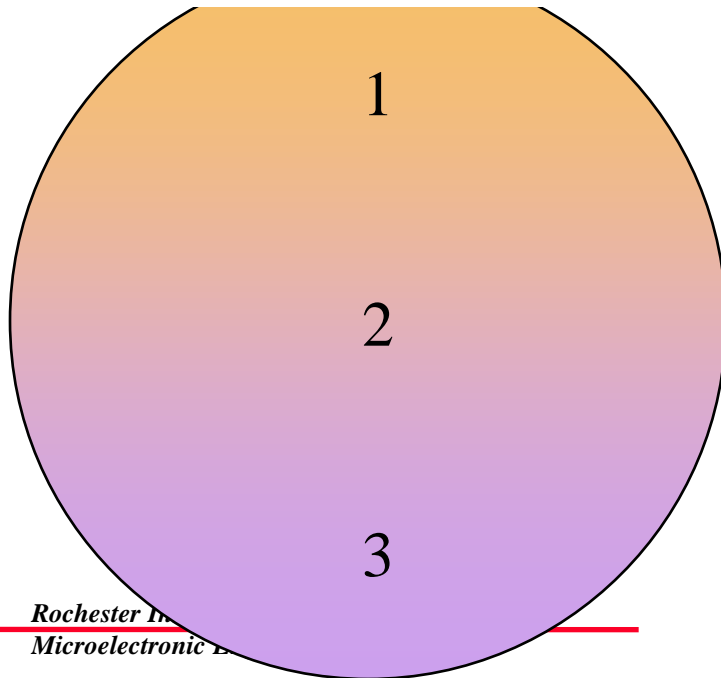


Rochester Institute of Technology
Microelectronic Engineering

NON UNIFORM OXIDE GROWTH PROBLEMS

Non uniform oxide growth (top different from bottom) is often caused by not having the door closed all the way against the tube allowing room air to mix with the gas in the furnace.

Top



10-10-01

Recipe 350 Tube 3

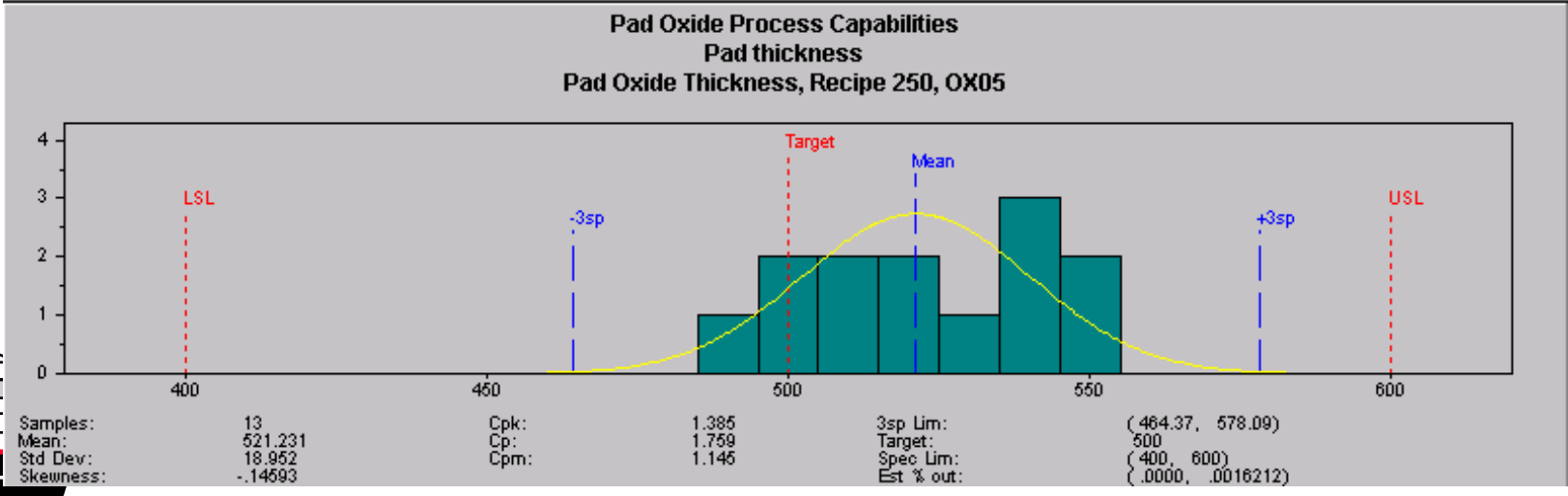
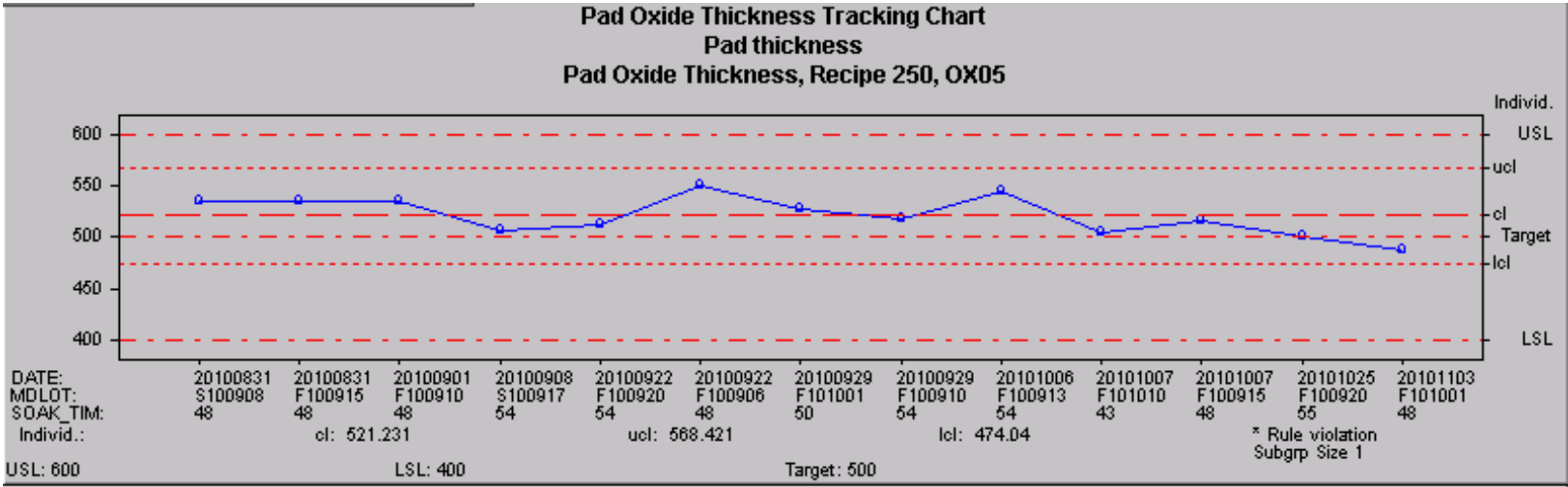
Target 5000 Å

Point 1 = 3980 Å

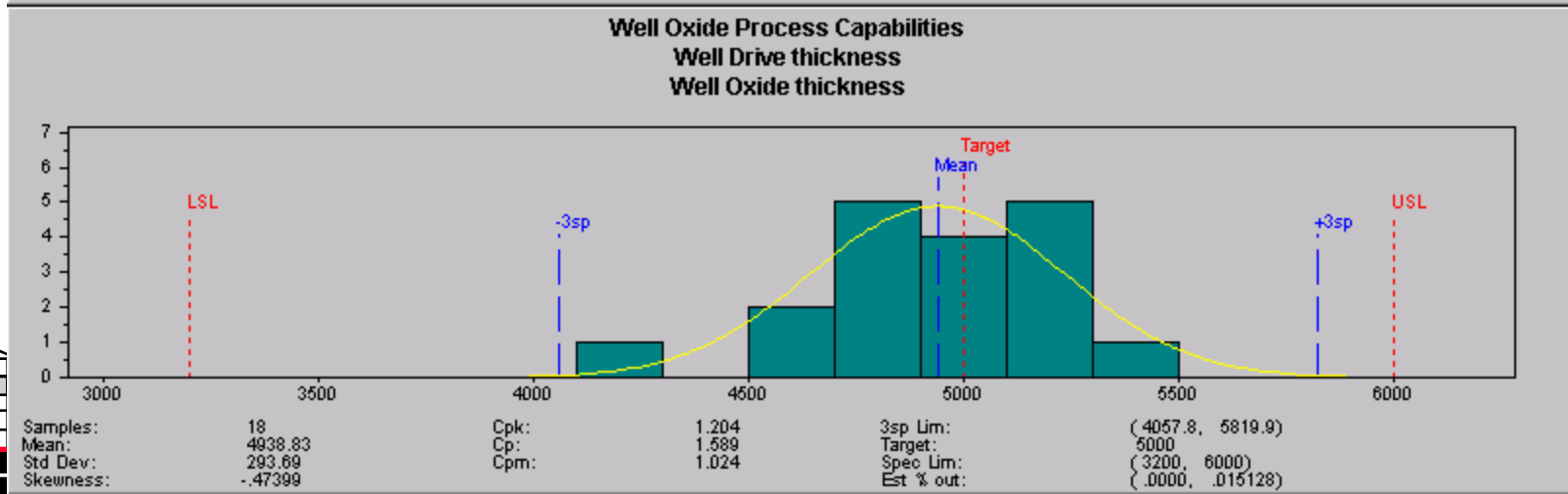
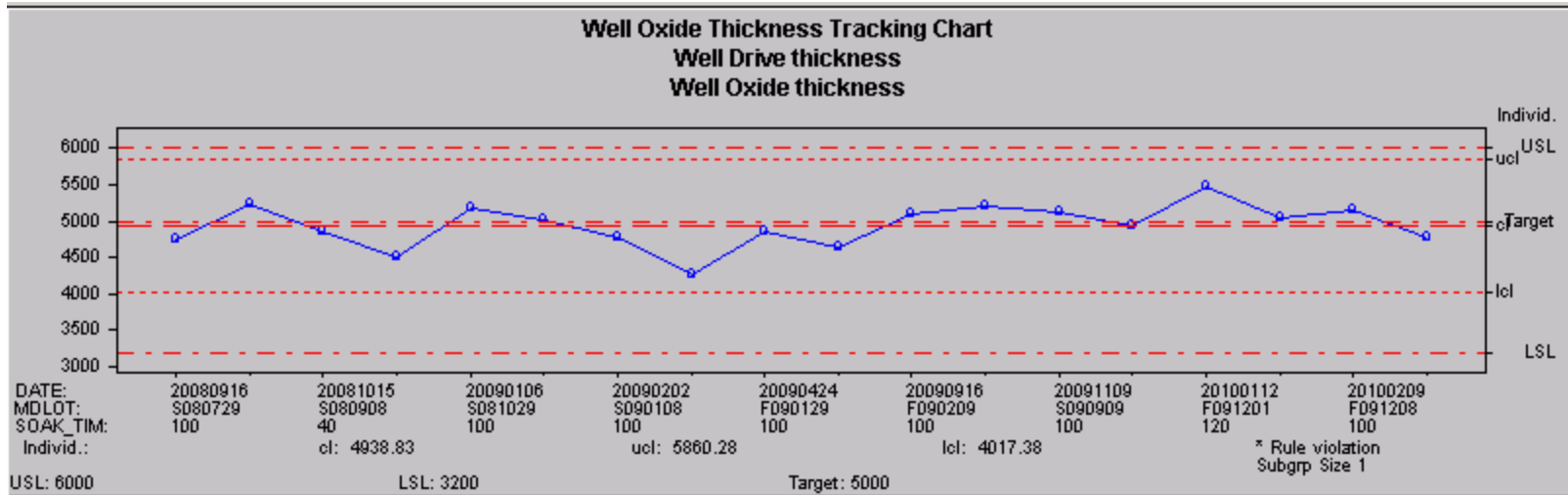
Point 2 = 3350 Å

Point 3 = 2997 Å

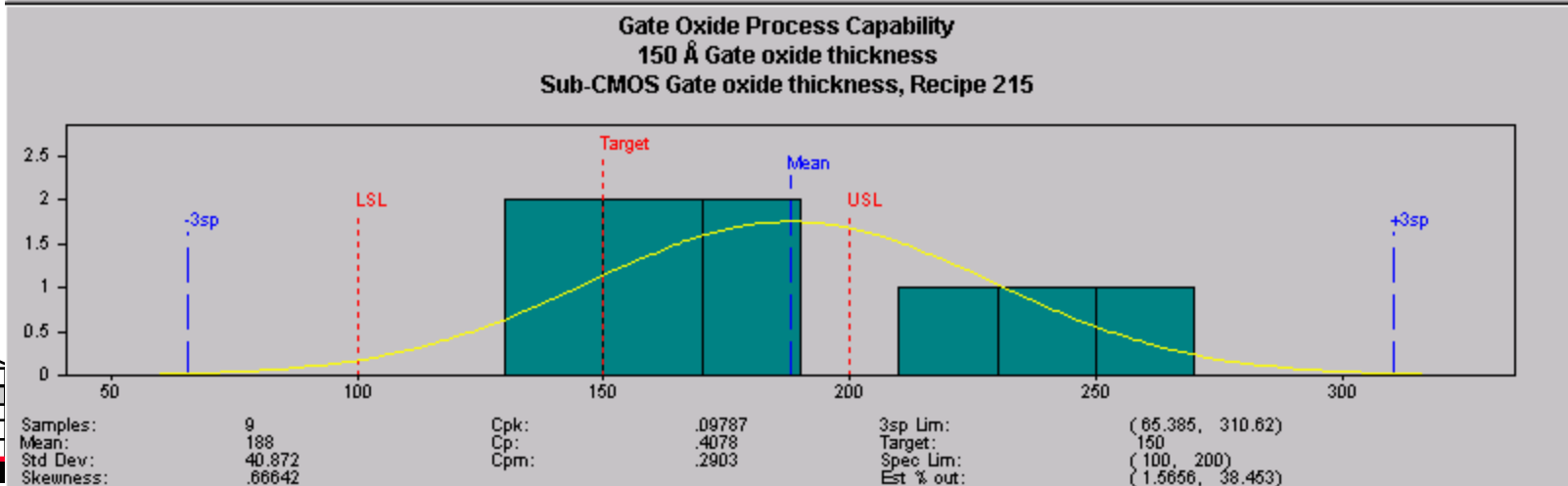
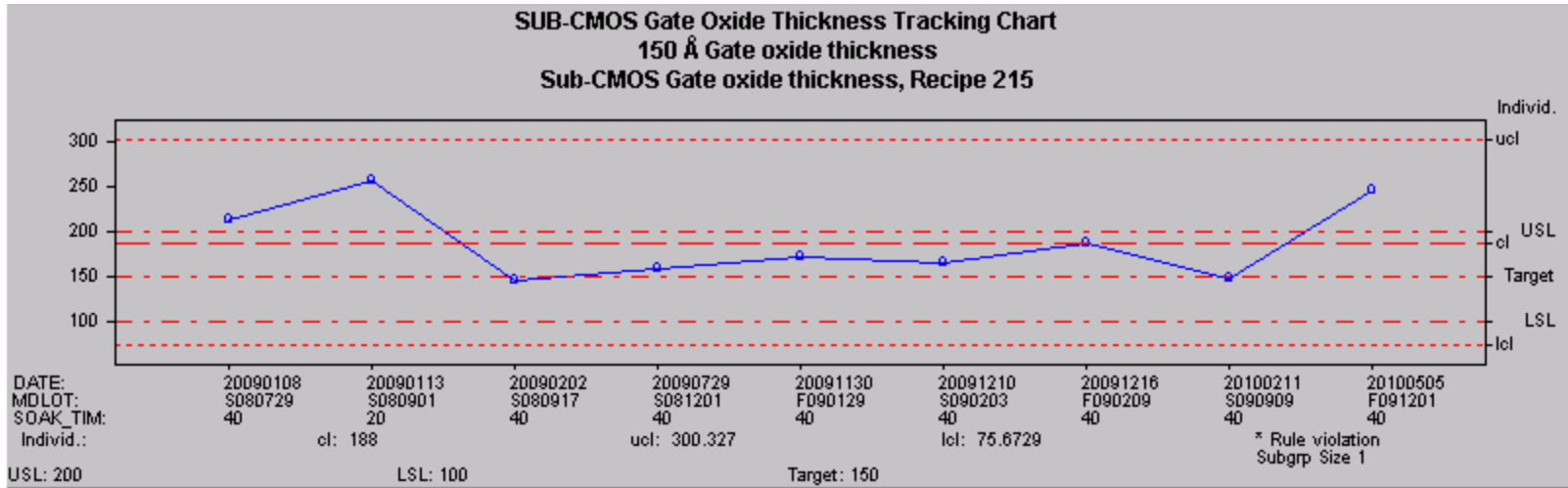
PAD OXIDE - SPC CHART



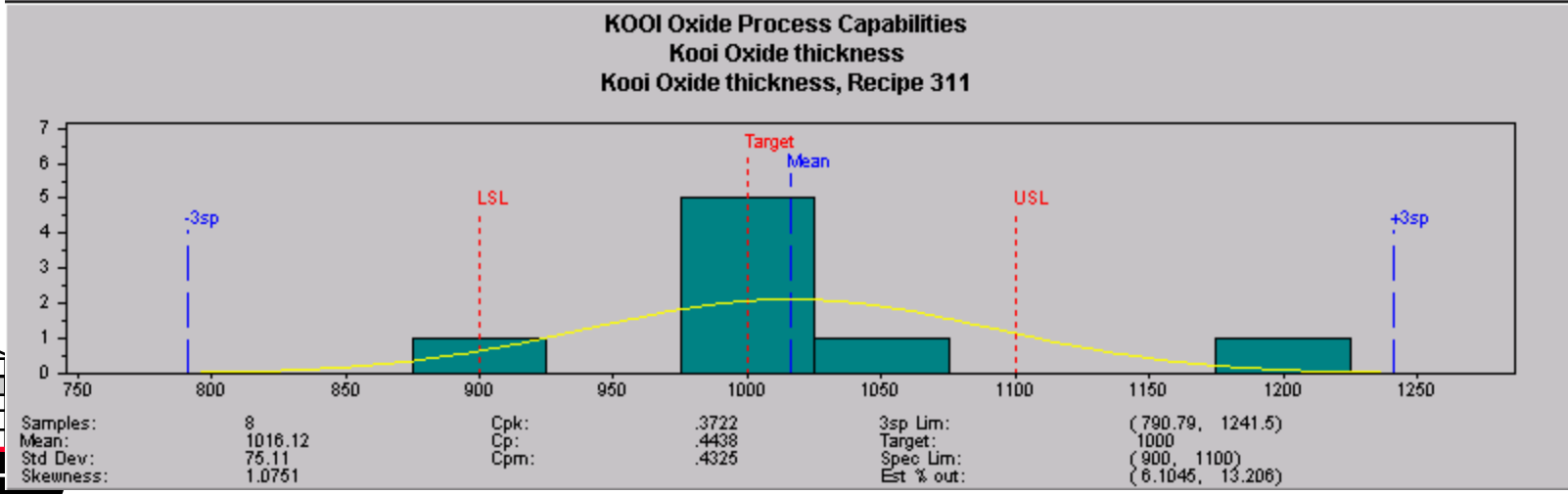
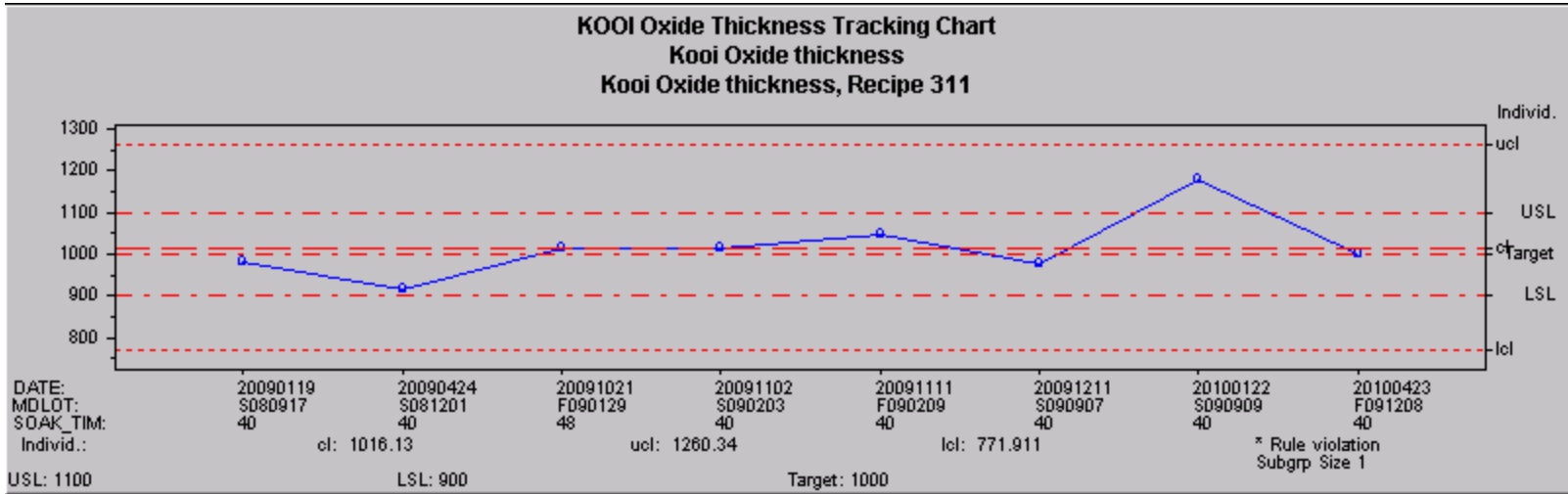
WELL OXIDE – SPC CHART



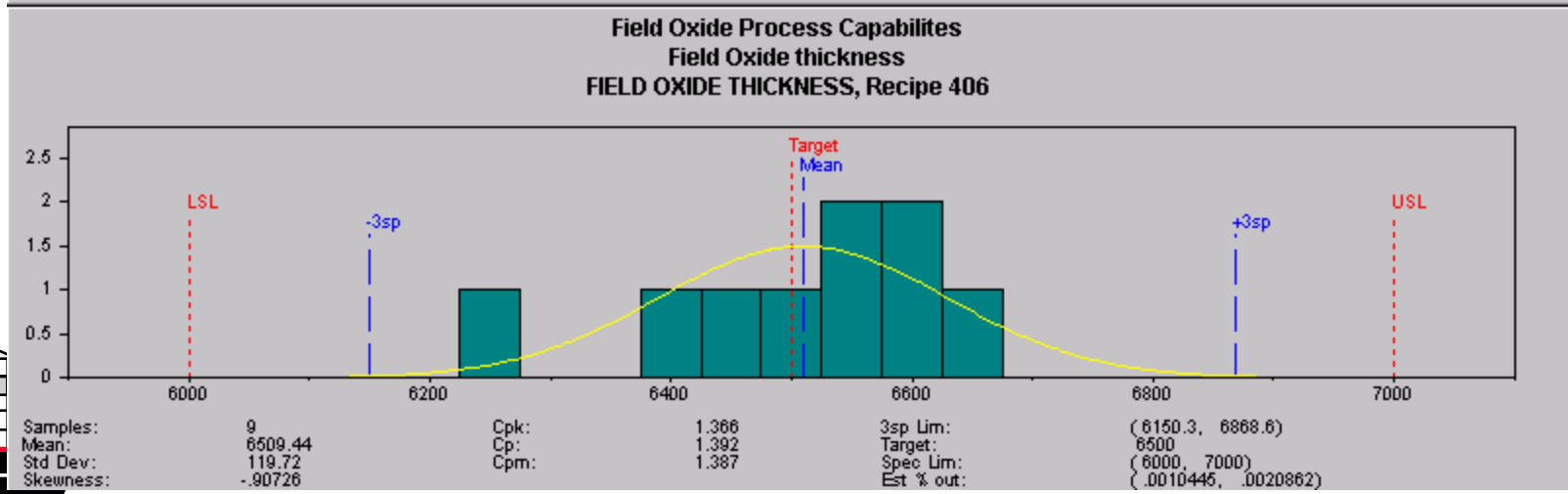
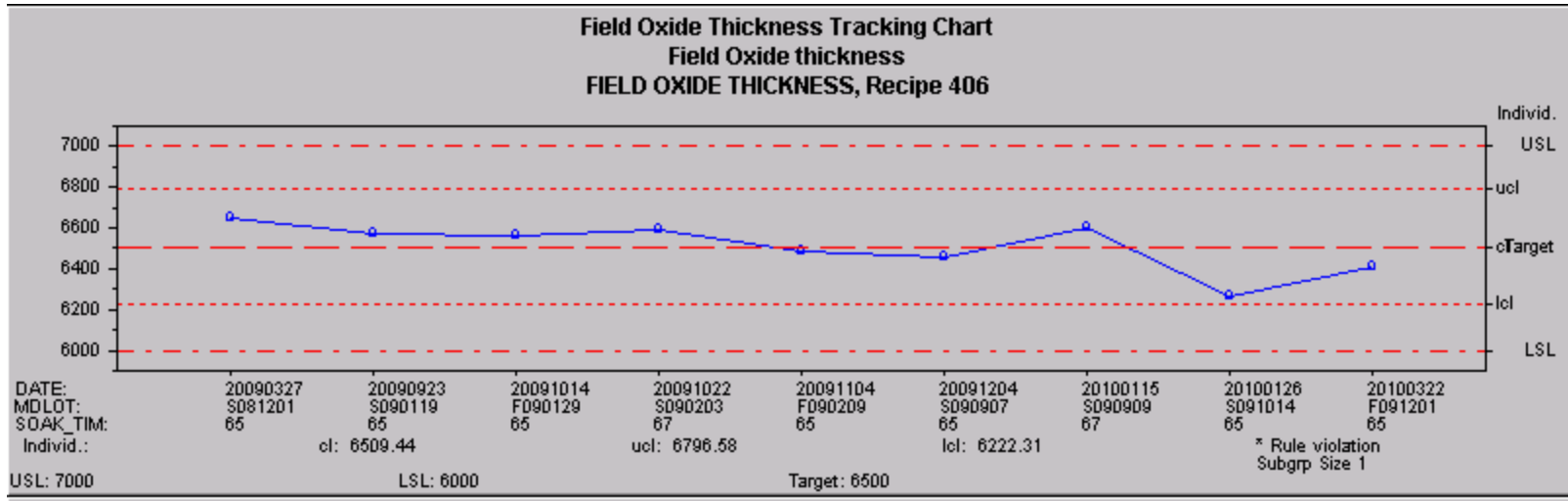
GATE OXIDE – SPC CHART



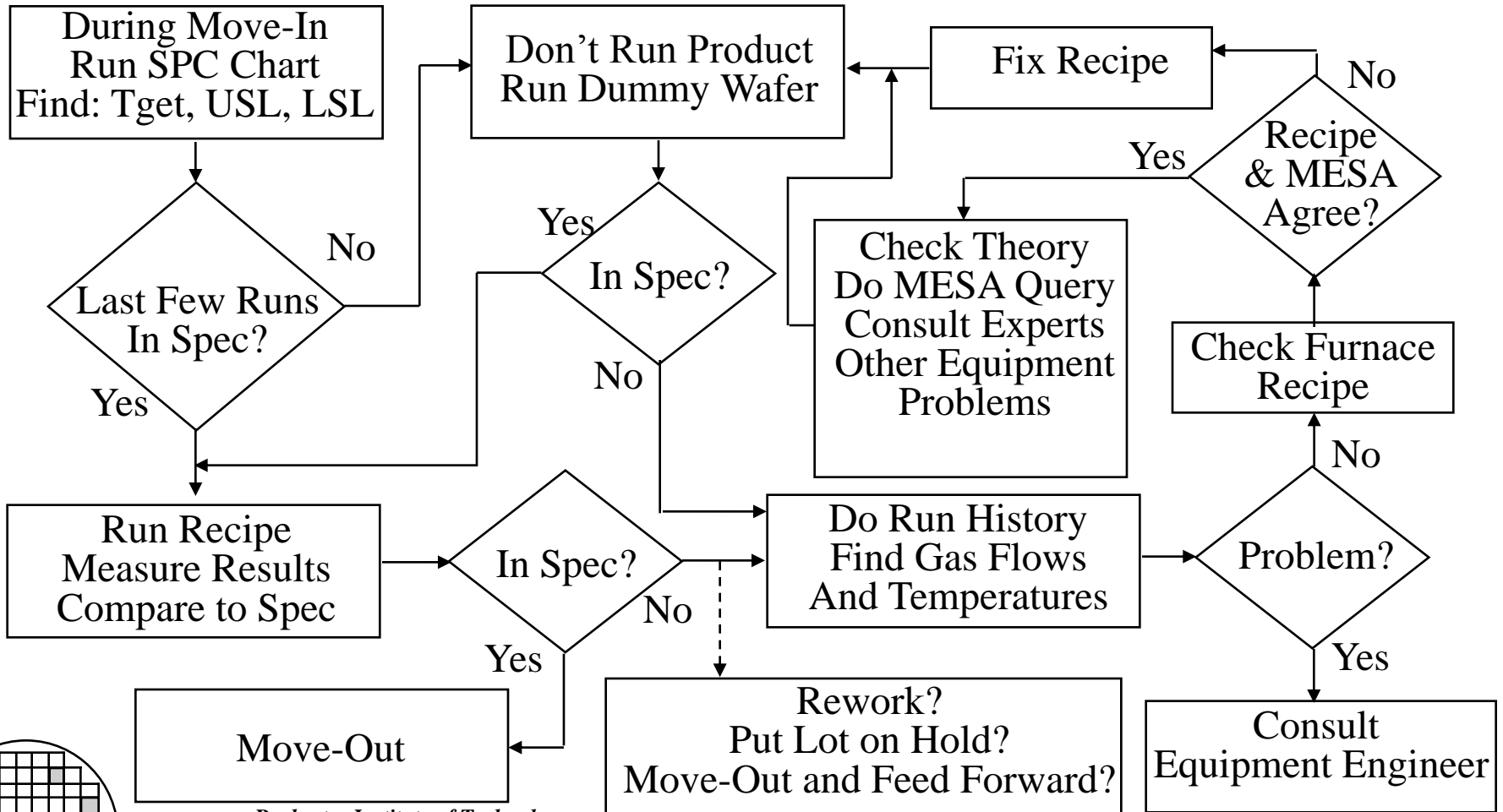
KOOI OXIDE – SPC CHART



FIELD OXIDE – SPC CHART



OUT OF CONTROL ACTION PLAN



***BAKE OF SPIN-ON DOPANT
200 °C FOR 15 MIN.***

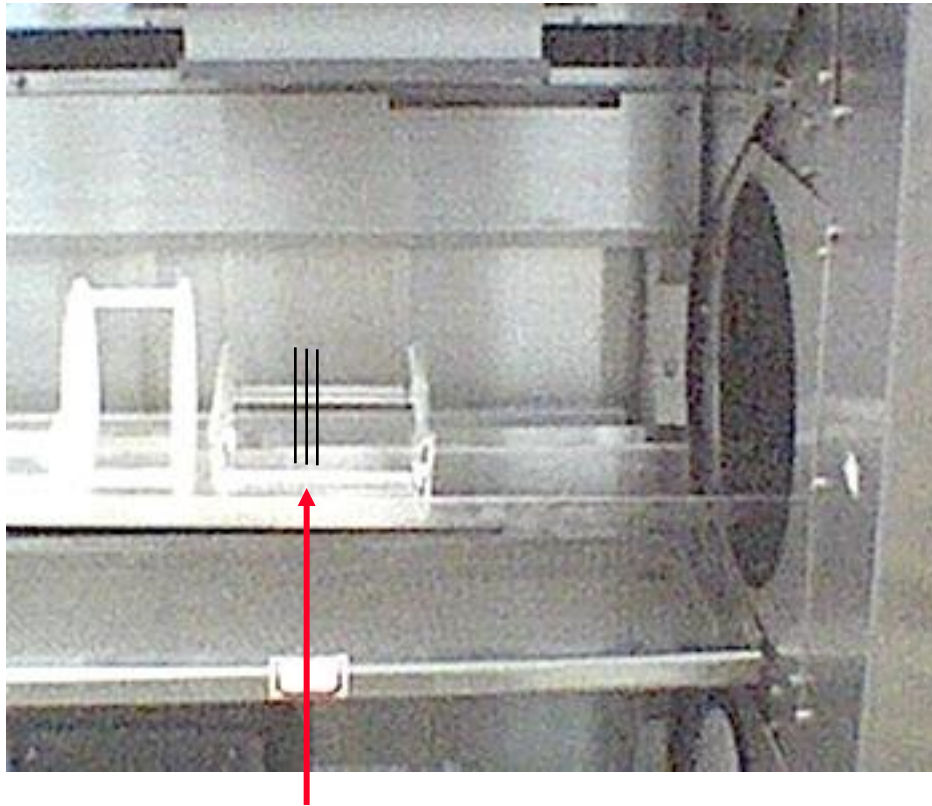


Use quartz boat from furnace tube you plan to use.

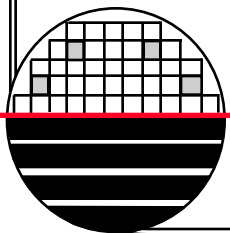
Use holder as shown because the boat will be hot.

Do not heat wafers with photoresist on them above 150 °C

POSITION OF WAFERS ON PADDLE



Load wafers here, when paddle is fully out.
Do not use dummy filler wafers...
the improved uniformity is negligible.



CREATING NEW RECIPES

Log In as engineer

Find a similar recipe

Edit > Copy > new recipe name



Pick a number that has not been used

Make changes

save

LIST OF RECIPES FOR BRUCE FURNACE

- 10 Lfull Sub CMOS Well, 1100 °C, 600 min, N2
- 11 Lfull Adv CMOS Well, 1100 °C, 360 min, N2
- 15 Lfull Well-Oxide, 1100 °C, 330 min, N2 + 25 min wet Oxide
- 16 Lfull TEOS Densification, 1hr. 1000°C, N2
- 99 Lfull Sinter, 400°C, 30min, N2/H2
- 101 Lfull Sinter, 450 °C, 30min, N2/H2
- 105 Lfull 1000 °C Anneal, 100 min, N2 only
- 106 Lfull Anneal sub-micron CMOS process, 900 °C, 30 min., N2
- 110 Lfull PMOS D/S Diffusion and Wet Ox, N2 then Wet O2
- 111 Lfull P+ Doping + Wet O2
- 115 Lfull N+ Doping + Wet O2
- 119 Lfull N+ Doping Thick Poly
- 120 Lfull N+ Poly Doping from Spin-on Source, 1000 °C, 15 min, N2
- 144 Lfull 1000°C Source/Drain Anneal

LIST OF RECIPES FOR BRUCE FURNACE

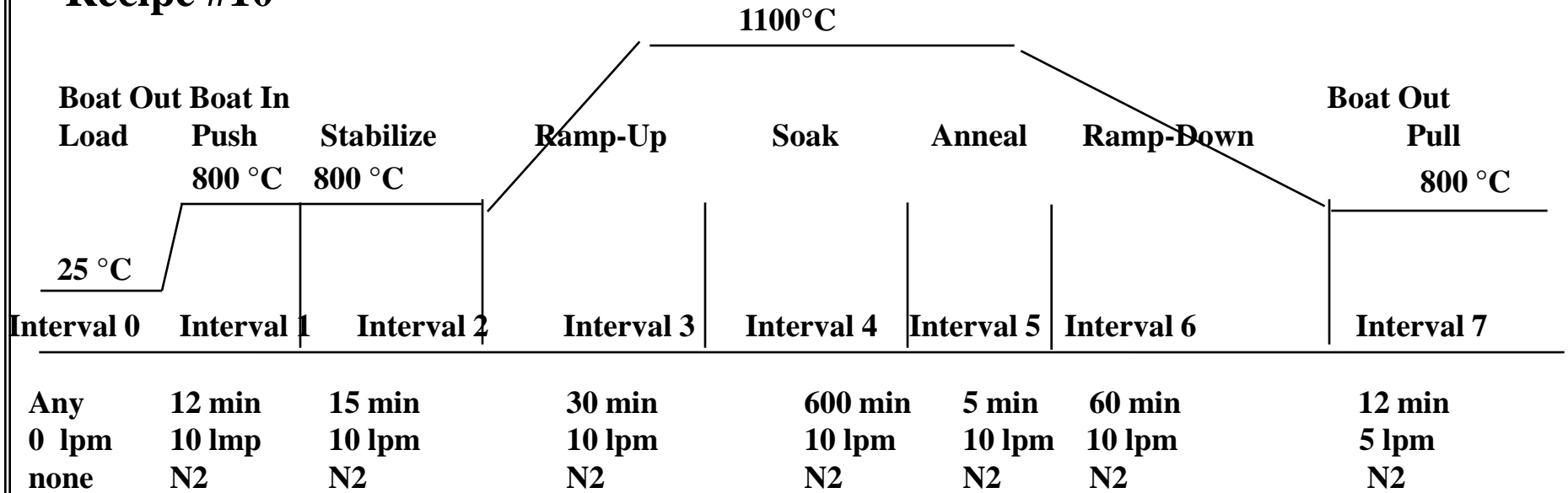
- 162 Lfull Well Drive SMFL-CMOS 25hr, 1100°C, N2
 163 Lfull SMFL-CMOS Field Oxide, 6500Å, 950°C, Wet Oxide
 175 Lfull Poly ReOxide 850°C, Wet Oxide, 15 min.
 180 Lfull Well Drive P-well CMOS, 6 hrs O2, 30 hrs N2, 1100 °C
 210 Lfull 100Å Gate Oxide
 213 Lfull 100Å Gate Oxide with N2O
 215 Lfull 150Å Gate Oxide, 900 °C, 50 min, Dry O2
 225 Lfull 250Å Gate Oxide
 250 Lfull 500Å Dry Oxide, 1000 °C, 56 min., soak, Gate/Pad Ox
 252 Lfull Dry Oxide Var Time, 1000 °C Set your own soak time
 270 Lfull 700Å Dry Oxide, 1Hr. 24min. 1000 °C soak
 280 Lfull D/S Implant Anneal, 1000 °C, 20 min N2 +10 min Wet O2
 284 Lfull D/S Anneal, 1000 C, 25 min. N2
 310 Lfull 1,000Å Dry Oxide, 2Hr. 18min. 1000 °C soak
 311 Lfull 1,000Å Kooi/Sacrificial Oxide, 900 °C, Wet O2, 40 min.

LIST OF RECIPES FOR BRUCE FURNACE

- 330 Lfull Wet 3,000 Å Wet Oxide, 1000 °C, 50 min. soak
- 336 Lfull Wet 3,650 Å Wet Oxide, 1000 °C, 55 min. soak
- 341 Lfull Wet 4,000 Å Wet Oxide, 1100 °C, 20 min. soak
- 350 Lfull Wet 5,000 Å Wet Oxide, 1000 °C, 100 min. soak
- 353 Short Course 5000 Å, 1100 °C, 45 min, Wet Ox
- 354 Short Course PreDep, 1050 °C, 5min N₂ + 5 min Wet Ox
- 355 Short Course Gate Ox, 1100 °C, 17min, Dry O₂
- 356 Short Course Sinter,
- 357 Short Course 8000 Å, 1100 °C, 95 min, Wet Ox
- 352 Lfull Wet Ox Var Time, 1100 °C, Set your own soak time
- 406 Lfull 6,500 Å Wet Oxide, Field Ox, 1100 °C, 65 min. soak
- 410 Lfull 10,000 Å Wet Oxide, Field Ox, 1100 °C, 210 min. soak
- 430 Lfull 30,000 Å Wet Oxide, Field Ox, 1100 °C, 15 Hr. soak
- 440 Lfull 40,000 Å Wet Oxide, Field Ox, 1100 °C, 35 Hr. soak
- 463 SMFL TransLC Tube Clean, Tube 4
- 474 Lfull SMFL CMOS 310 Å Gate Oxide, N₂/O₂, 1000C, 15 min.

BRUCE FURNACE RECIPE 10 SUB-CMOS WELL DRIVE

Recipe #10



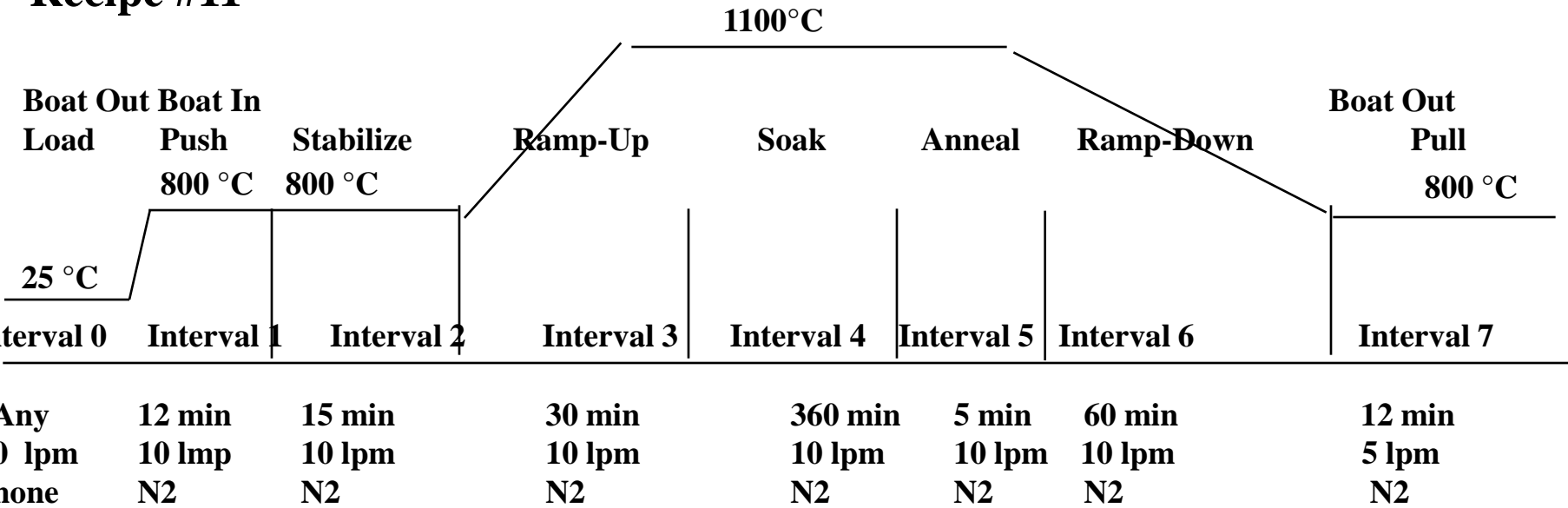
At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

Sub-CMOS Well Drive, No Oxide Growth, Tube 1

Rochester Institute of Technology
Microelectronic Engineering

BRUCE FURNACE RECIPE 11 ADV-CMOS WELL DRIVE

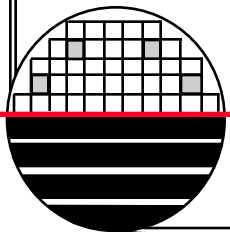
Recipe #11



At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

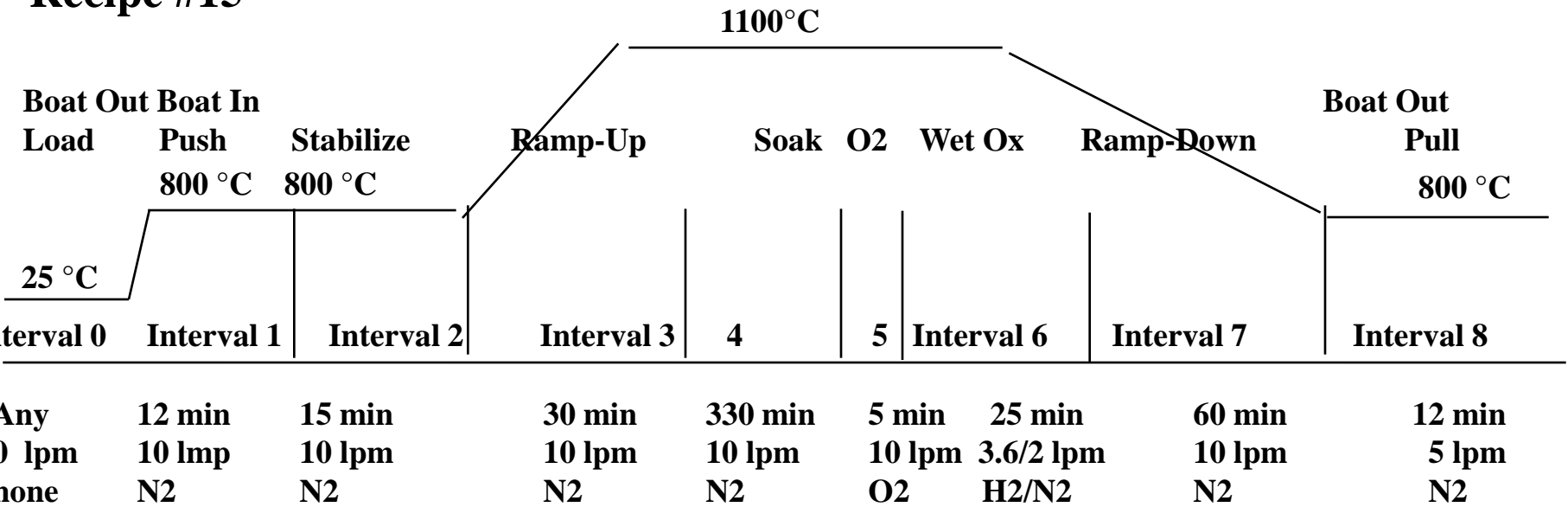
Adv-CMOS Well Drive, No Oxide Growth, Tube 1

*Rochester Institute of Technology
Microelectronic Engineering*



BRUCE FURNACE RECIPE 11 ADV-CMOS WELL DRIVE

Recipe #15



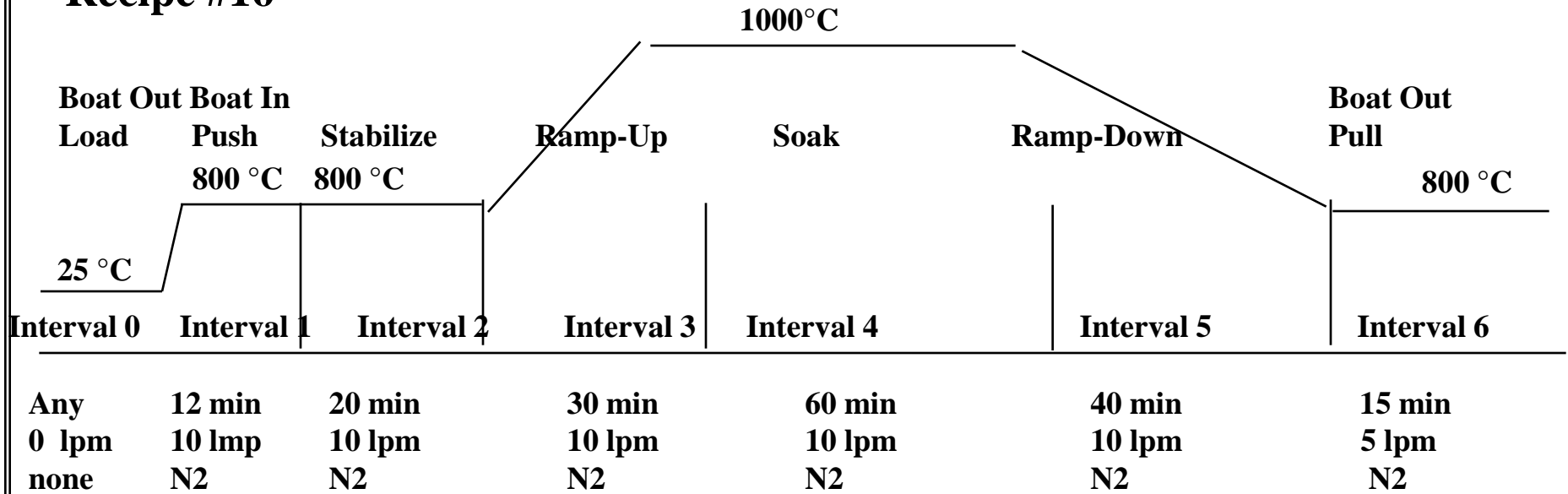
At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

CMOS Well Drive, 3000Å Wet Oxide Growth, Tube 1

Rochester Institute of Technology
Microelectronic Engineering

BRUCE FURNACE RECIPE 16 ADV-CMOS WELL DRIVE

Recipe #16



At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

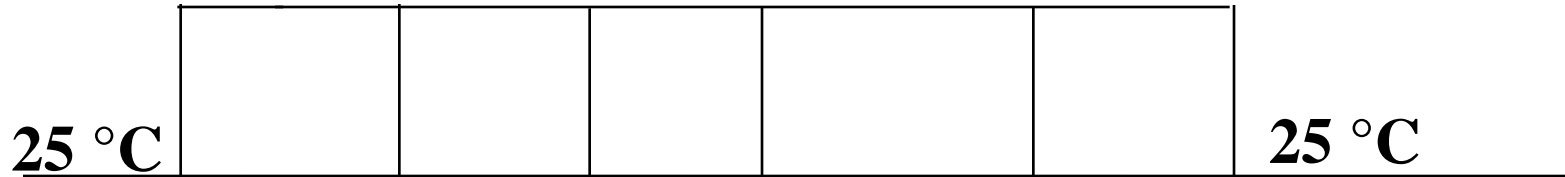
Adv-CMOS Well Drive, No Oxide Growth, Tube 1

Rochester Institute of Technology
Microelectronic Engineering

BRUCE FURNACE RECIPE 99 SINTER

SINTER Recipe #99

Warm Push Stabilize Soak Anneal Pull
 400°C



Interval 0	1	2	3	4	5	6
Any`	60	30	15	15	5	15 min
0 lpm	10	10	10	5	10	5 lpm
None	N2	N2	N2	N2/H2	N2	N2

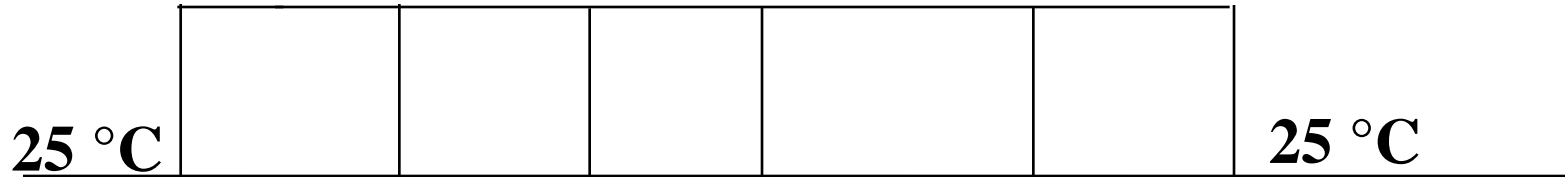
At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

BRUCE FURNACE RECIPE 101 SINTER

SINTER Recipe #101

Verified:8-20-08

Warm Push Stabilize Soak Purge Pull
450°C

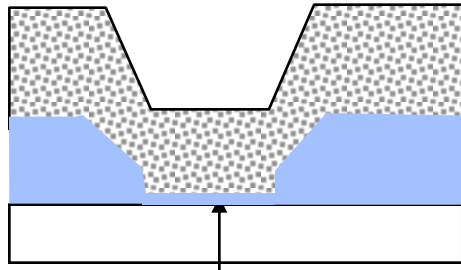


Interval 0	1	2	3	4	5	6	
Any`	60	30	15	15	5	15	min
0 lmp	10	10	10	5	10	5	lpm
None	N2	N2	N2/H2	N2/H2	N2	N2	

At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

SINTER

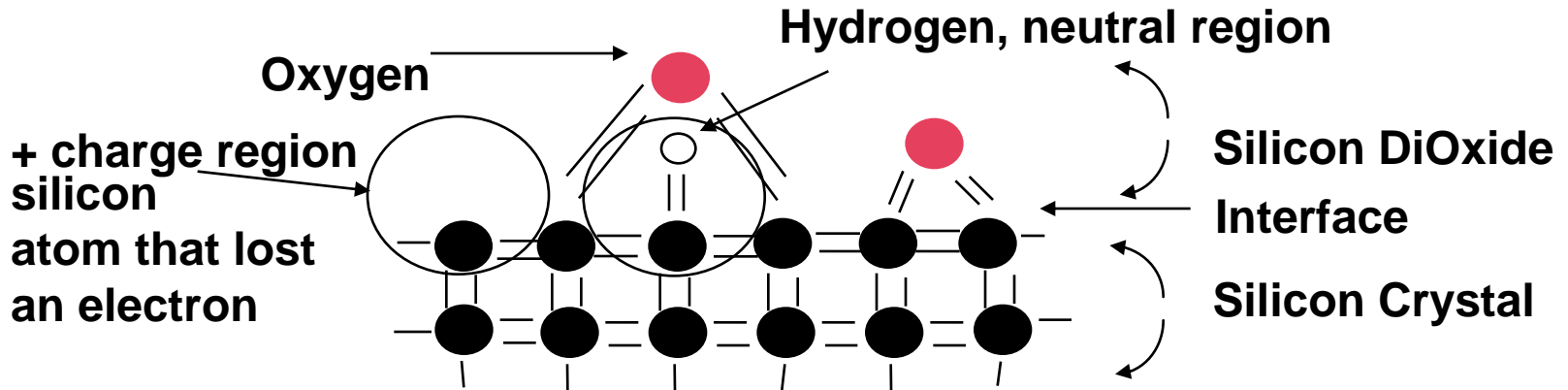
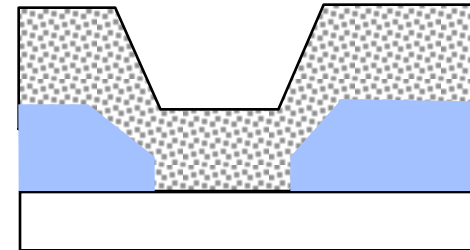
Before Sinter



Native Oxide

Reduce Contact Resistance

After Sinter

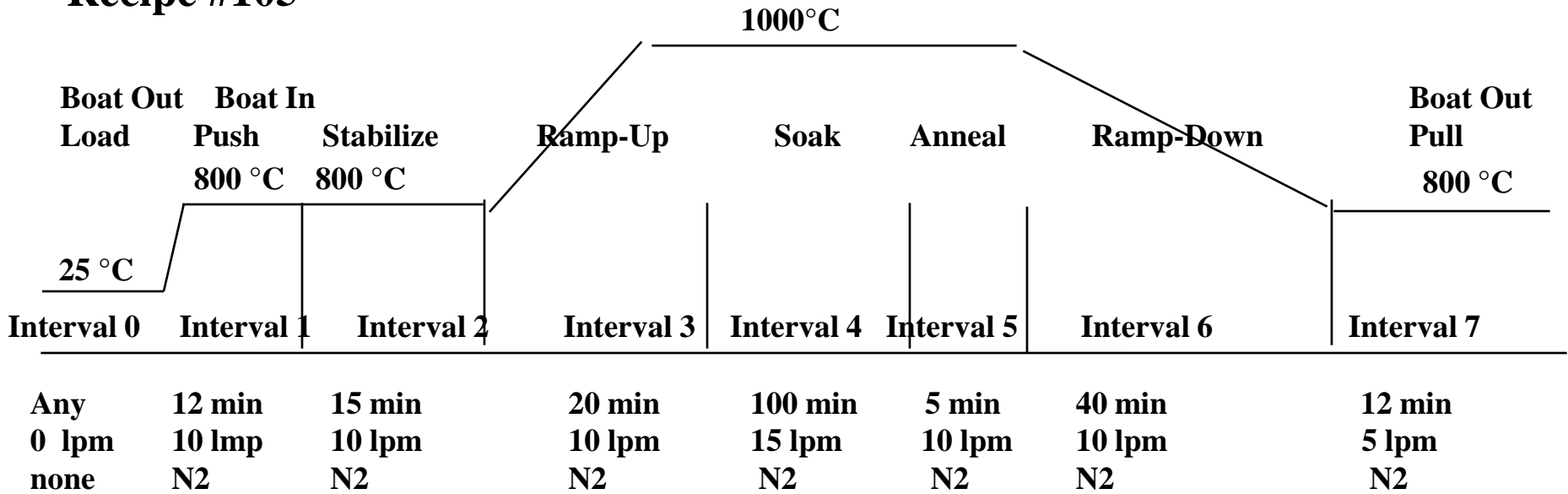


Reduce Surface States

BRUCE FURNACE RECIPE 105 – 1000°C ANNEAL

Recipe #105

Verified:2-24-04



At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

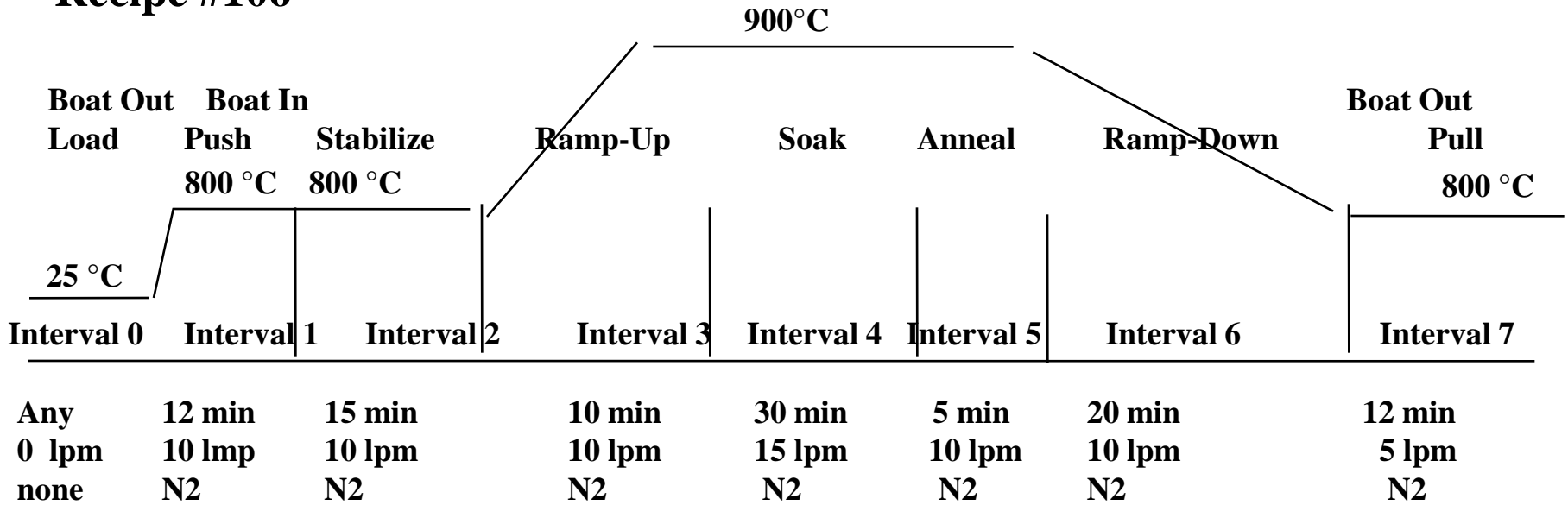
1000°C Anneal, No Oxide Growth

Rochester Institute of Technology
Microelectronic Engineering

BRUCE FURNACE RECIPE 106 – 900°C ANNEAL

Verified:2-24-04

Recipe #106



At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

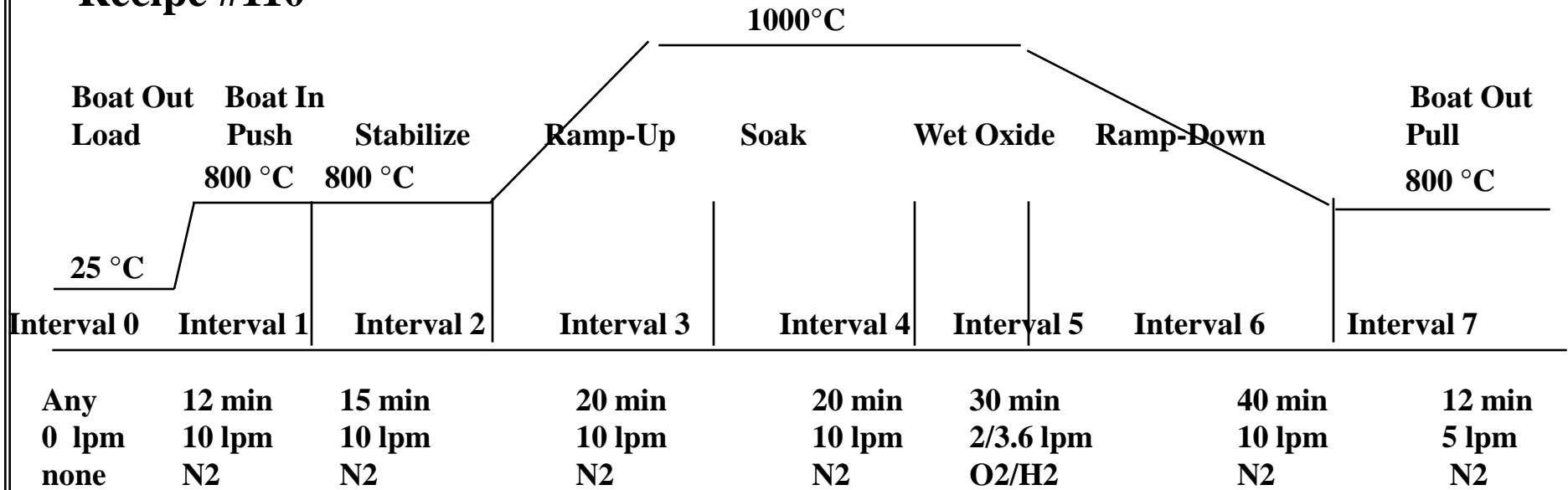
900°C Anneal, No Oxide Growth

Rochester Institute of Technology
Microelectronic Engineering

BRUCE FURNACE RECIPE 110 PMOS D/S & WET O2

Verified:2-24-04

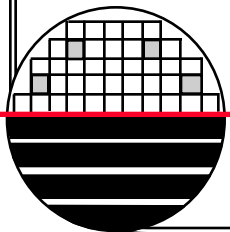
Recipe #110



At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

PMOS D/S Diffusion plus Wet Oxide Growth

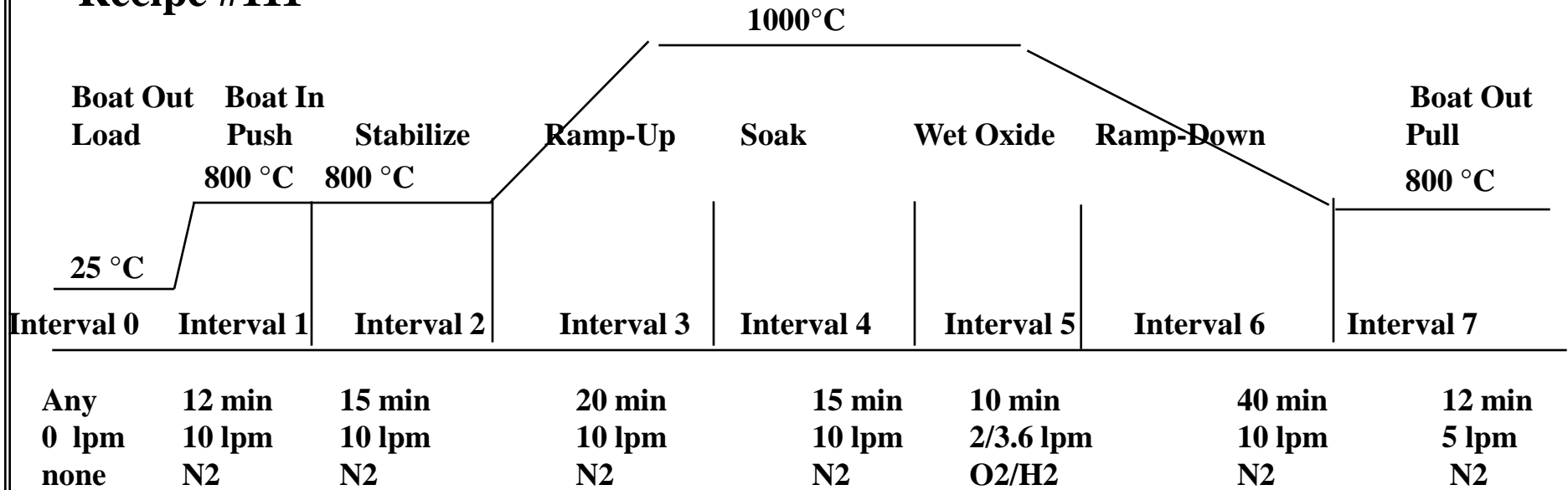
Rochester Institute of Technology
Microelectronic Engineering



BRUCE FURNACE RECIPE 111 P+ POLY DOPE

Verified:2-24-04

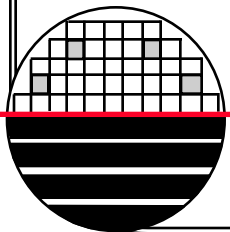
Recipe #111



At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

P-Type Poly Dope plus Wet Oxide Growth

Rochester Institute of Technology
Microelectronic Engineering



BRUCE FURNACE RECIPE 115 N+ DIFF & WET O2

Recipe #115

Verified:2-24-04

1000 °C



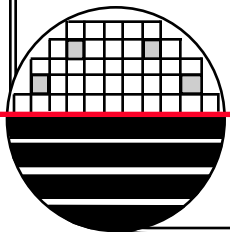
Boat Out Load	Boat In Push	Stabilize	Ramp-Up	Soak	Wet Oxide	Ramp-Down	Boat Out Pull
Interval 0	Interval 1	Interval 2	Interval 3	Interval 4	Interval 5	Interval 6	Interval 7
25 °C	800 °C	800 °C					800 °C

Any	12 min	15 min	20 min	30 min	30 min	40 min	12 min
0 lpm	10 lpm	10 lpm	10 lpm	10 lpm	2/3.6 lpm	10 lpm	5 lpm
none	N2	N2	N2	N2	O2/H2	N2	N2

At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

N+ Diffusion plus Wet Oxide Growth, Target 2854 Å

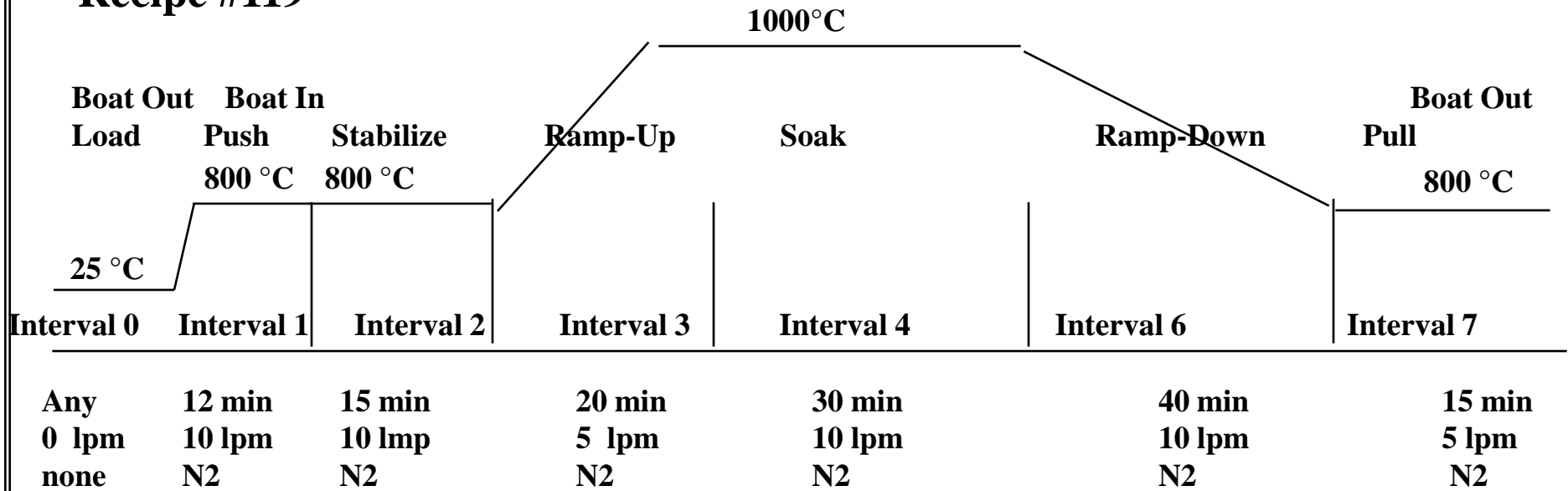
Rochester Institute of Technology
Microelectronic Engineering



BRUCE FURNACE RECIPE 119 – N++ POLY DOPE

Verified:2-24-04

Recipe #119



At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

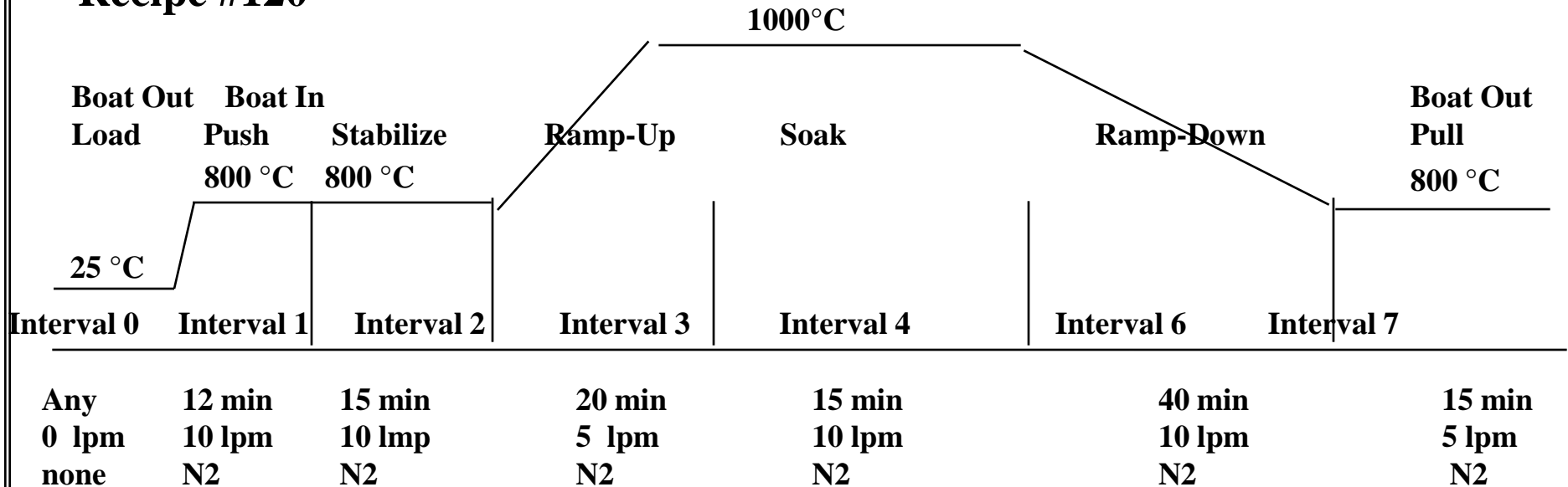
N+ Poly Doping, Thick Poly, > 1 μm, No Oxide Growth

Rochester Institute of Technology
Microelectronic Engineering

BRUCE FURNACE RECIPE 120- N+ POLY DOPE

Verified:2-24-04

Recipe #120



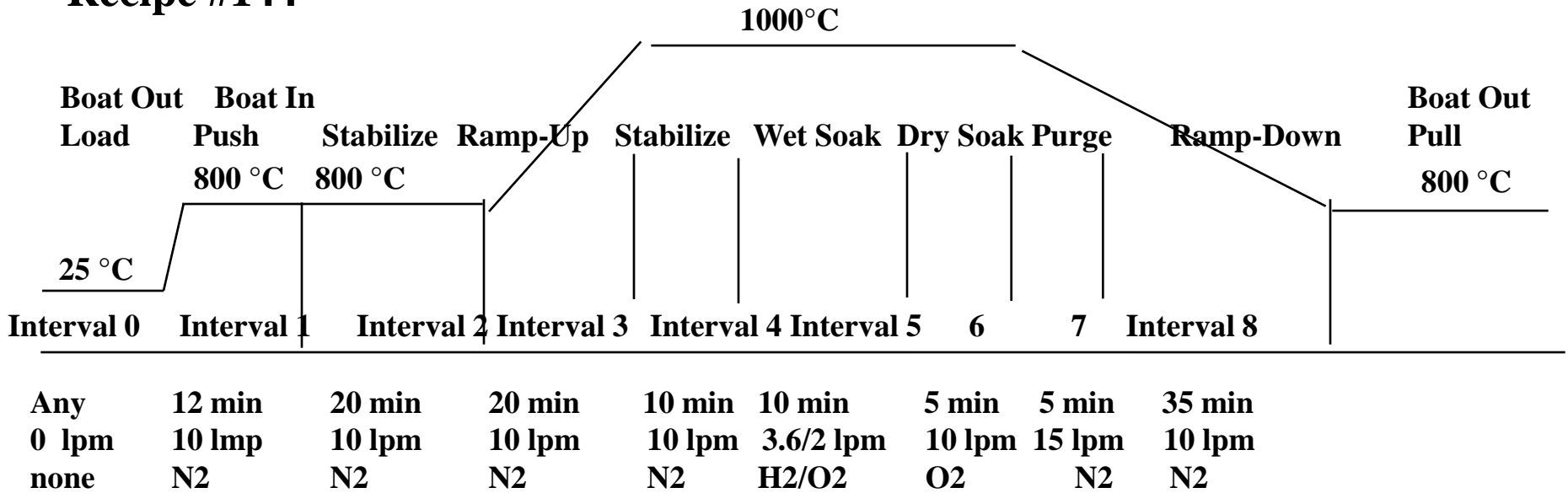
At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

N+ Poly Doping, Thin Poly, < 1 μm, No Oxide Growth

Rochester Institute of Technology
Microelectronic Engineering

BRUCE FURNACE RECIPE 144 – 1000°C S/D ANNEAL

Recipe #144



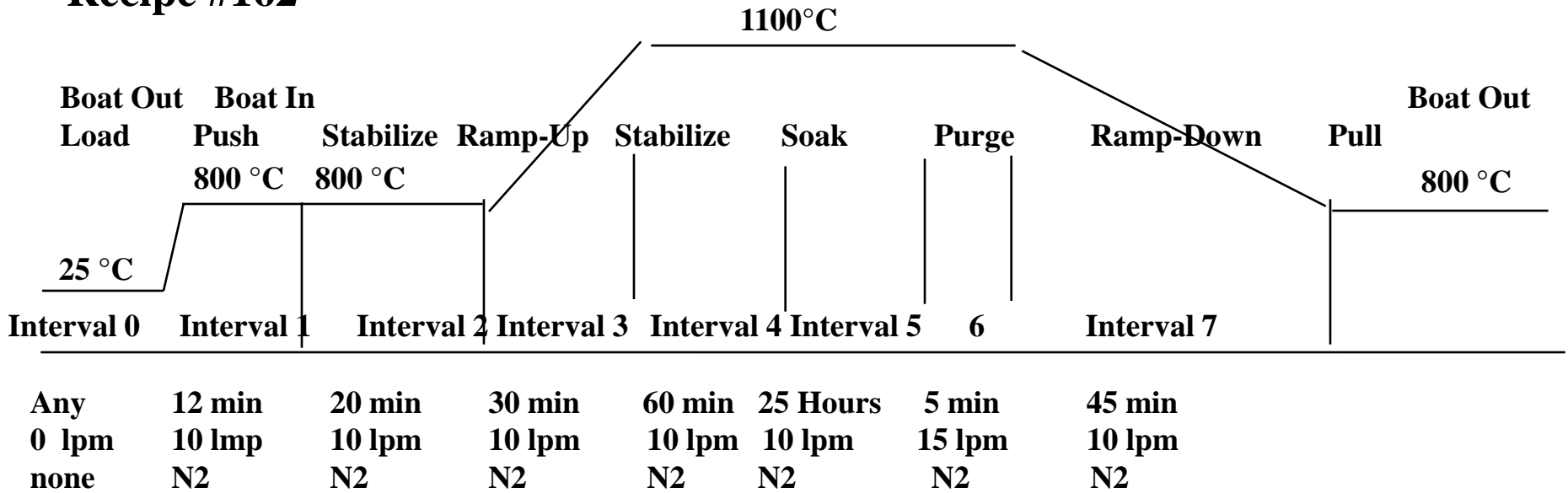
At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

1000°C Anneal, With Oxide Growth

Rochester Institute of Technology
Microelectronic Engineering

BRUCE FURNACE RECIPE 162 – 1100°C 25HR WELL DRIVE

Recipe #162



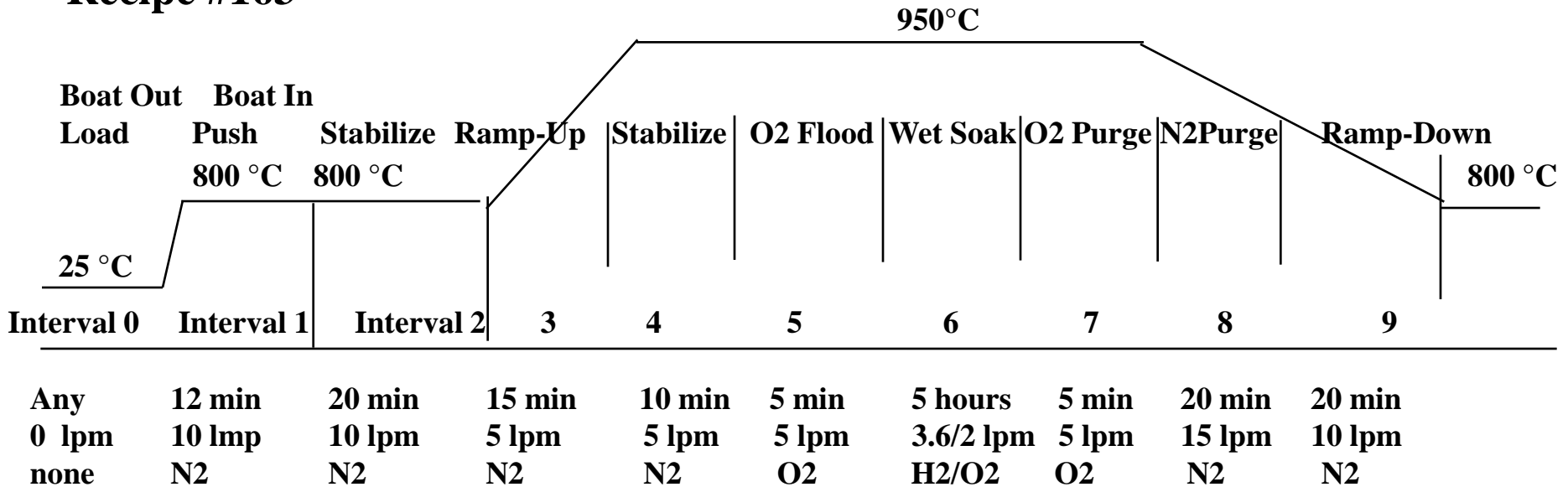
At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

1100°C Well Drive, No Oxide Growth

Rochester Institute of Technology
Microelectronic Engineering

BRUCE FURNACE RECIPE 163 – 950°C 6500Å FIELD OX

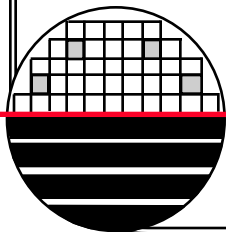
Recipe #163



At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

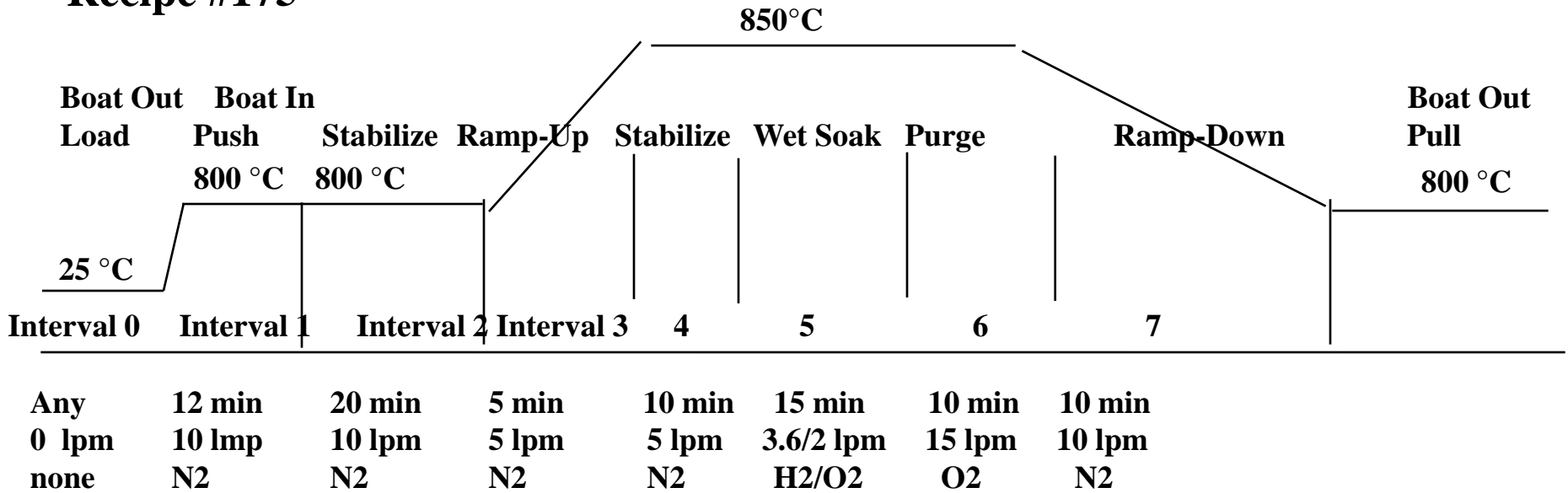
950°C Wet Oxide Growth, Target 6500Å

Rochester Institute of Technology
Microelectronic Engineering



BRUCE FURNACE RECIPE 175 – 850°C POLY REOX

Recipe #175



At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

850°C Poly Reoxide

Rochester Institute of Technology
Microelectronic Engineering

BRUCE FURNACE RECIPE 180 – P-WELL DRIVE

Verified:2-24-04

Recipe #180

1100 °C

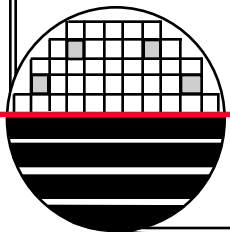


Interval 0	Interval 1	Interval 2	Interval 3	Interval 4	Interval 5	Interval 6	Interval 7
Any	12 min	15 min	30 min	6 hr	30 hr	60 min	15 min
0 lpm	10 lpm	10 lpm	5 lpm	10 lpm	15 lpm	10 lpm	5 lpm
none	N2	N2	O2	O2	N2	N2	N2

At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

P-well CMOS Drive and Oxide Growth

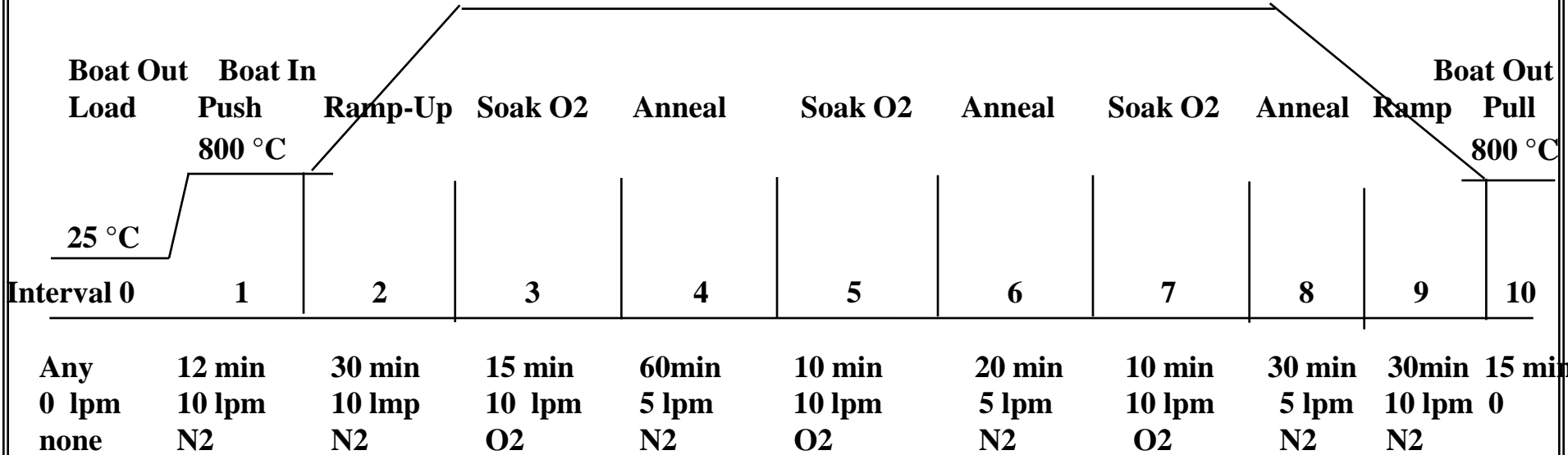
Rochester Institute of Technology
Microelectronic Engineering



BRUCE FURNACE RECIPE 210 – TUNNEL OXIDE

Recipe #210

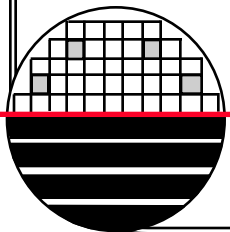
950 °C



At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

Tunnel Oxide for EEPROM, Target 100 Å

Rochester Institute of Technology
Microelectronic Engineering



BRUCE FURNACE RECIPE 213 100 Å DRY OXIDE

Verified:2-24-04

Recipe #213

900°C

Boat Out Load

Boat In Push

Stabilize

Ramp-Up

Soak

Soak

Ramp-Down

Boat Out Pull

Pull

800 °C

800 °C

800 °C

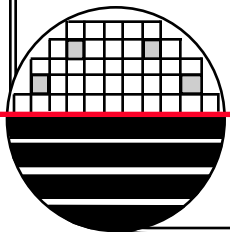
25 °C

Interval 0	Interval 1	Interval 2	Interval 3	Interval 4	Interval 5	Interval 6	Interval 7
Any	12 min	30 min	30 min	30 min	30 min	30 min	15 min
0 lpm	5 lpm	5 lpm	10 lpm	10 lpm	10 lpm	10 lpm	5 lpm
none	N2	N2	O2	N2O	O2	N2	N2

At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

Dry Oxide Growth with N2O, Target 100 Å

Rochester Institute of Technology
Microelectronic Engineering

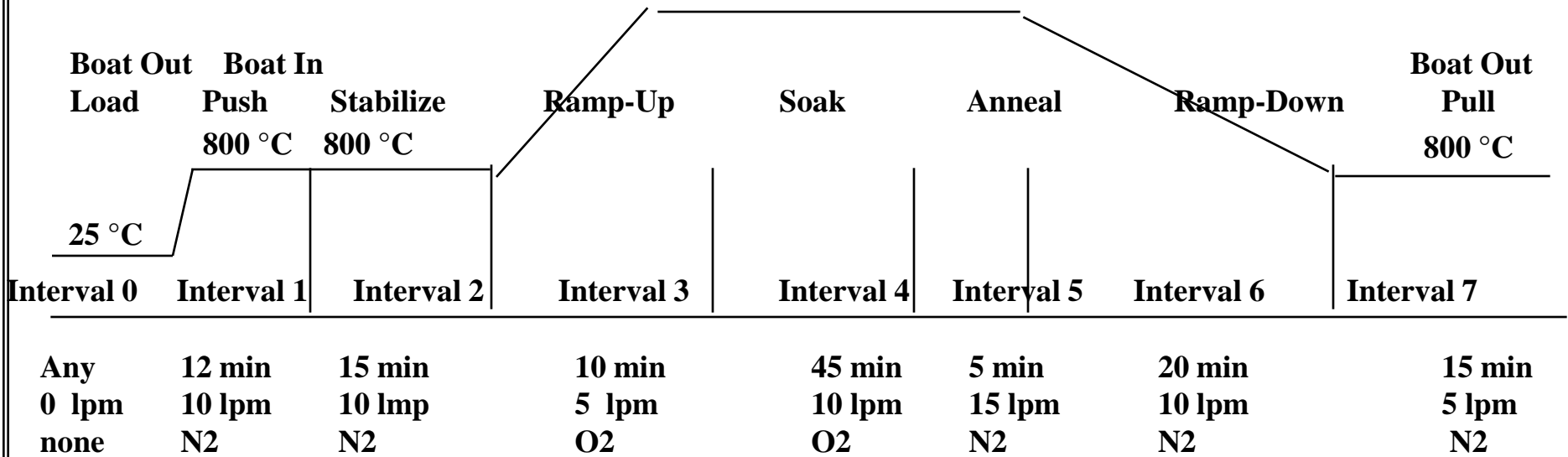


BRUCE FURNACE RECIPE 215 – 150Å DRY OXIDE

Verified:2-24-04

Recipe #215

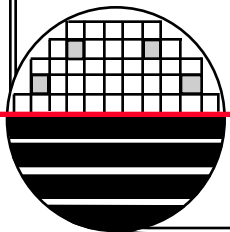
900 °C



At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

Dry Oxide Growth, Target 150 Å

Rochester Institute of Technology
Microelectronic Engineering



BRUCE FURNACE RECIPE 225 – 250 Å DRY OXIDE

Verified:2-24-04

Recipe #225

900 °C

Boat Out Load
Boat In Push
800 °C

Stabilize
800 °C

Ramp-Up

Soak

Anneal

Ramp-Down

Boat Out Pull
800 °C

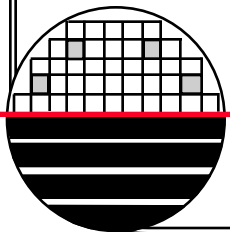
25 °C

Interval 0	Interval 1	Interval 2	Interval 3	Interval 4	Interval 5	Interval 6	Interval 7
Any	12 min	15 min	10 min	93 min	5 min	20 min	15 min
0 lpm	10 lpm	10 lpm	5 lpm	10 lpm	15 lpm	10 lpm	5 lpm
none	N2	N2	O2	O2	N2	N2	N2

At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

Dry Oxide Growth, Target 250 Å

Rochester Institute of Technology
Microelectronic Engineering



BRUCE FURNACE RECIPE 250 - 500Å DRY OXIDE

Verified:2-24-04

Recipe #250

1000°C

Boat Out Load
Boat In Push
800 °C

Stabilize
800 °C

Ramp-Up

Soak

Anneal

Ramp-Down

Boat Out Pull
800 °C

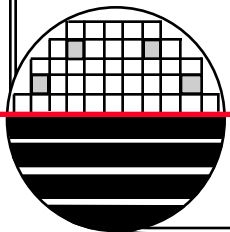
25 °C

Interval 0	Interval 1	Interval 2	Interval 3	Interval 4	Interval 5	Interval 6	Interval 7
Any	12 min	15 min	20 min	56 min	5min	40 min	12 min
0 lpm	10 lpm	10 lpm	5 lpm	10 lpm	15 lpm	10 lpm	5 lpm
none	N2	N2	O2	O2	N2	N2	N2

At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

Dry Oxide Growth, Target 500 Å

Rochester Institute of Technology
Microelectronic Engineering

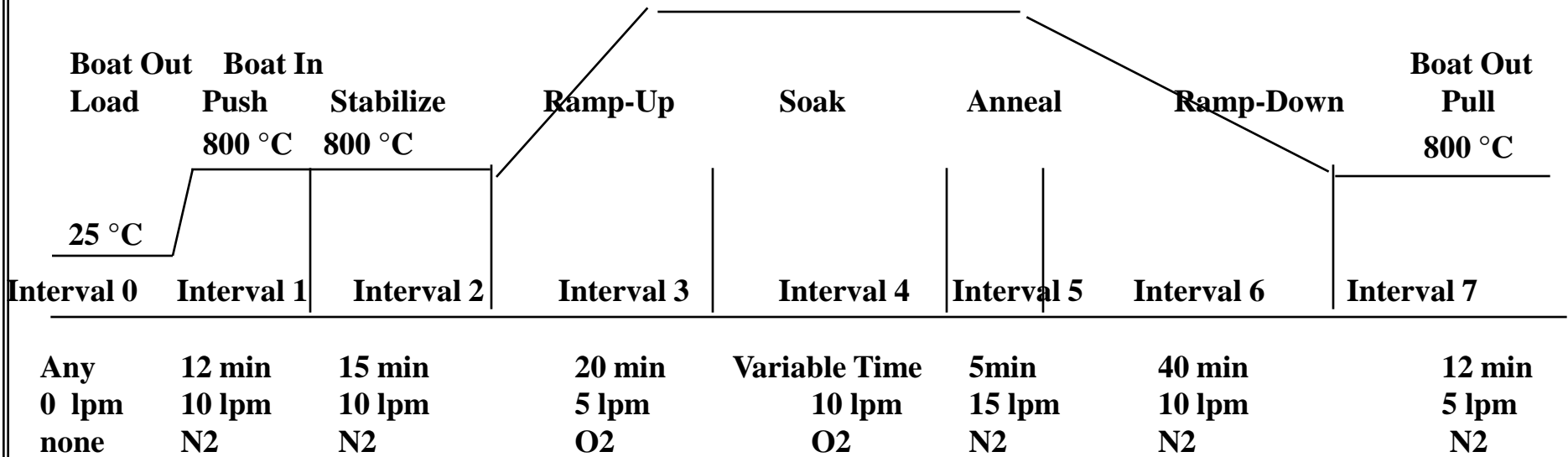


BRUCE FURNACE RECIPE 252 - VARIABLE DRY OXIDE

Verified:2-24-04

Recipe #252

1000°C



At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

Dry Oxide Growth, Variable Target

Rochester Institute of Technology
Microelectronic Engineering

BRUCE FURNACE RECIPE 270 – 700Å DRY OXIDE

Verified: 3-1-04

Recipe #270

1000°C

Boat Out Load
Boat In Push
800 °C

Stabilize
800 °C

Ramp-Up

Soak

Anneal

Ramp-Down

Boat Out Pull
800 °C

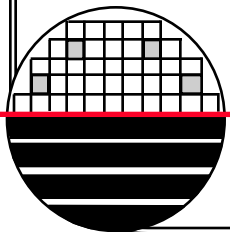
25 °C

Interval 0	Interval 1	Interval 2	Interval 3	Interval 4	Interval 5	Interval 6	Interval 7
Any	12 min	15 min	20 min	93 min	5 min	40 min	15 min
0 lpm	10 lpm	10 lpm	5 lpm	10 lpm	15 lpm	10 lpm	5 lpm
none	N2	N2	O2	O2/	N2	N2	N2

At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

Dry Oxide Growth, Target 700 Å

Rochester Institute of Technology
Microelectronic Engineering



BRUCE FURNACE RECIPE 280 – Sub-CMOS ANNEAL

Recipe #280

1000°C

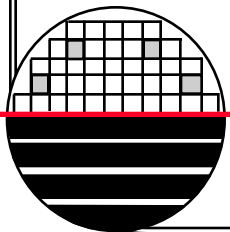


Interval 0	Interval 1	Interval 2	Interval 3	Interval 4	Interval 5	Interval 6	Interval 7
Any	12 min	15 min	20 min	20 min	5 min	40 min	15 min
0 lpm	10 lpm	10 lpm	5 lpm	10 lpm	15 lpm	10 lpm	5 lpm
none	N2	N2	O2	O2/	N2	N2	N2

At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

DS Implant Anneal, Oxide Growth

Rochester Institute of Technology
Microelectronic Engineering



BRUCE FURNACE RECIPE 284 – Adv-CMOS ANNEAL

Recipe #284

1000°C

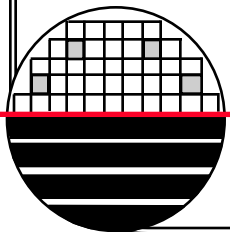


Interval 0	Interval 1	Interval 2	Interval 3	Interval 4	Interval 5	Interval 6	Interval 7
Any	12 min	15 min	20 min	20 min	5 min	40 min	15 min
0 lpm	10 lpm	10 lpm	5 lpm	10 lpm	15 lpm	10 lpm	5 lpm
none	N2	N2	N2	N2	N2	N2	N2

At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

DS Implant Anneal, Oxide Growth

Rochester Institute of Technology
Microelectronic Engineering



BRUCE FURNACE RECIPE 310 – DRY OXIDE 1,000Å

Recipe #310

1000°C

Boat Out Load
Boat In Push
800 °C

Stabilize
800 °C

Ramp-Up/O2 Purge

Soak

Anneal

Ramp-Down

Boat Out Pull
800 °C

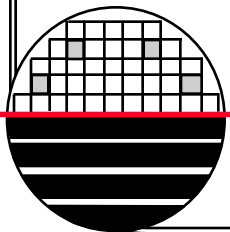
25 °C

Interval 0	Interval 1	Interval 2	Interval 3	Interval 4	Interval 5	Interval 6	Interval 7
Any	12 min	15 min	20 min	138 min	5 min	35 min	15 min
0 lpm	10 lpm	10 lpm	5 lpm	10 lpm	15 lpm	10 lpm	5 lpm
none	N2	N2	O2	O2	N2	N2	N2

At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

Dry Oxide Growth, Target 1000 Å

Rochester Institute of Technology
Microelectronic Engineering



BRUCE FURNACE RECIPE 311 – WET OXIDE 1,000Å

Recipe #311

900°C

Boat Out Load
Boat In Push
800 °C

Stabilize
800 °C

Ramp-Up/O2 Purge

Soak

Anneal

Ramp-Down

Boat Out Pull
800 °C

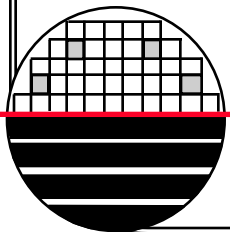
25 °C

Interval 0	Interval 1	Interval 2	Interval 3	4	Interval 5	Interval 6	Interval 7	Interval 8
Any	12 min	15 min	10 min	5 min	40 min	5 min	15 min	15 min
0 lpm	10 lpm	10 lpm	5 lpm	10 lpm	3.6/2.0 lpm	15 lpm	10 lpm	5 lpm
none	N2	N2	O2	O2	O2/H2	N2	N2	N2

At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

Wet Oxide Growth, Target 1000 Å, Kooi

Rochester Institute of Technology
Microelectronic Engineering



BRUCE FURNACE RECIPE 330 – WET OXIDE 3,000Å

Recipe #330 Lfull 3000 A Wet Ox

1000°C

Boat Out Load

Boat In Push

Stabilize

Ramp-Up

Flood

Soak

Anneal

Ramp-Down

Boat Out Pull

800 °C

800 °C

800 °C

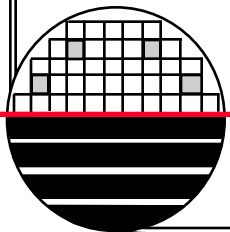
25 °C

Interval 0	Interval 1	Interval 2	Interval 3	Interval 4	Interval 5	Interval 6	Interval 7	Interval 8
Any	12 min	15 min	20 min	5 min	50 min	5 min	40 min	12 min
0 lpm	10 lpm	10 lpm	5 lpm	10 lpm	3.6/2.0 lpm	15 lpm	10 lpm	5 lpm
none	N2	N2	N2	O2	O2/H2	N2	N2	N2

At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

Wet Oxide Growth, Target 3000 Å

Rochester Institute of Technology
Microelectronic Engineering



BRUCE FURNACE RECIPE 336 – WET OXIDE 3,650Å

Recipe #336 Lfull 3650 A Wet Ox

1000°C

Boat Out Load Boat In Push Stabilize Ramp-Up Flood Soak Anneal Ramp-Down Boat Out Pull

800 °C 800 °C 800 °C

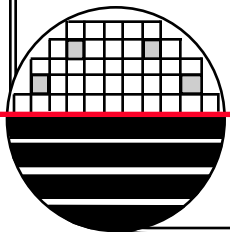
25 °C

Interval 0	Interval 1	Interval 2	Interval 3	Interval 4	Interval 5	Interval 6	Interval 7	Interval 8
Any	12 min	15 min	20 min	5 min	55 min	5 min	40 min	12 min
0 lpm	10 lpm	10 lpm	5 lpm	10 lpm	3.6/2.0 lpm	15 lpm	10 lpm	5 lpm
none	N2	N2	N2	O2	O2/H2	N2	N2	N2

At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

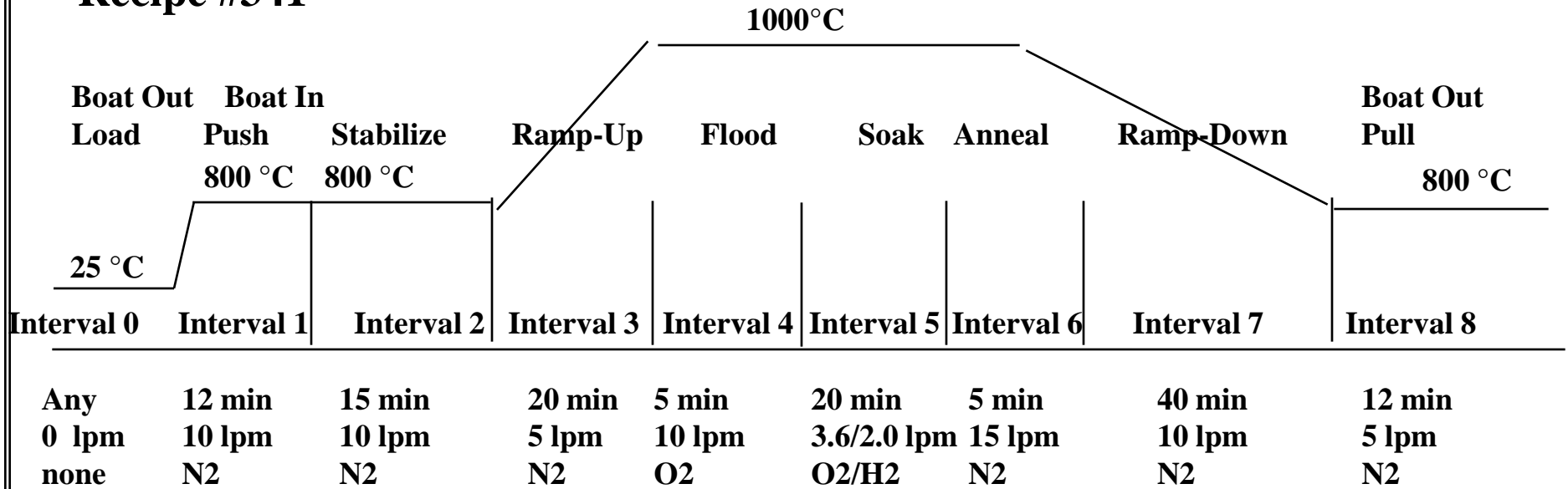
Wet Oxide Growth, Target 3650 Å

Rochester Institute of Technology
Microelectronic Engineering



BRUCE FURNACE RECIPE 341 – WET OXIDE 4,000Å

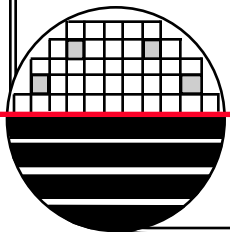
Recipe #341



At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

Wet Oxide Growth, Target 4000 Å

Rochester Institute of Technology
Microelectronic Engineering



BRUCE FURNACE RECIPE 350 – WET OXIDE 5,000Å

Recipe #350

1000°C

Boat Out Load Boat In Push Stabilize Ramp-Up Flood Soak Anneal Ramp-Down Boat Out Pull

800 °C 800 °C 800 °C

25 °C

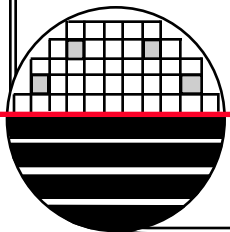
800 °C

Interval 0	Interval 1	Interval 2	Interval 3	Interval 4	Interval 5	Interval 6	Interval 7	Interval 8
Any	12 min	15 min	20 min	5 min	100 min	5 min	40 min	12 min
0 lpm	10 lpm	10 lpm	5 lpm	10 lpm	3.6/2.0 lpm	15 lpm	10 lpm	5 lpm
none	N2	N2	N2	O2	O2/H2	N2	N2	N2

At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

Wet Oxide Growth, Target 5000 Å

Rochester Institute of Technology
Microelectronic Engineering



**BRUCE FURNACE RECIPE 352 – WET OXIDE
VARIABLE THICKNESS**

Recipe #352

1000 °C

Boat Out Load Boat In Push Stabilize Ramp-Up Flood Soak Anneal Ramp-Down Boat Out Pull

800 °C 800 °C 800 °C

25 °C

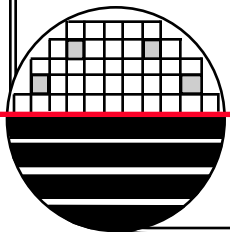
800 °C

Interval 0	Interval 1	Interval 2	Interval 3	Interval 4	Interval 5	Interval 6	Interval 7	Interval 8
Any	12 min	15 min	20 min	5 min	??? min	5 min	40 min	12 min
0 lpm	10 lpm	10 lpm	5 lpm	5 lpm	10 lpm	15 lpm	10 lpm	15 lpm
none	N2	N2	N2	O2	O2/H2	N2	N2	N2

At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

Wet Oxide Growth, Variable Target

Rochester Institute of Technology
Microelectronic Engineering



BRUCE FURNACE RECIPE 406 – WET OXIDE 6,500Å

Recipe #406

1100°C

Boat Out Load
Boat In Push
800 °C

Stabilize
800 °C

Ramp-Up

Soak

Anneal

Ramp-Down

Boat Out Pull
800 °C

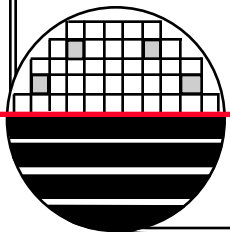
25 °C

Interval 0	Interval 1	Interval 2	Interval 3	Interval 4	Interval 5	Interval 6	Interval 7	Interval 8
Any	12 min	15 min	30 min	5 min	65 min	5 min	60 min	12 min
0 lpm	10 lpm	10 lpm	5 lpm	5 lpm	10 lpm	15 lpm	10 lpm	15 lpm
none	N2	N2	N2	O2	O2/H2	N2	N2	N2

At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

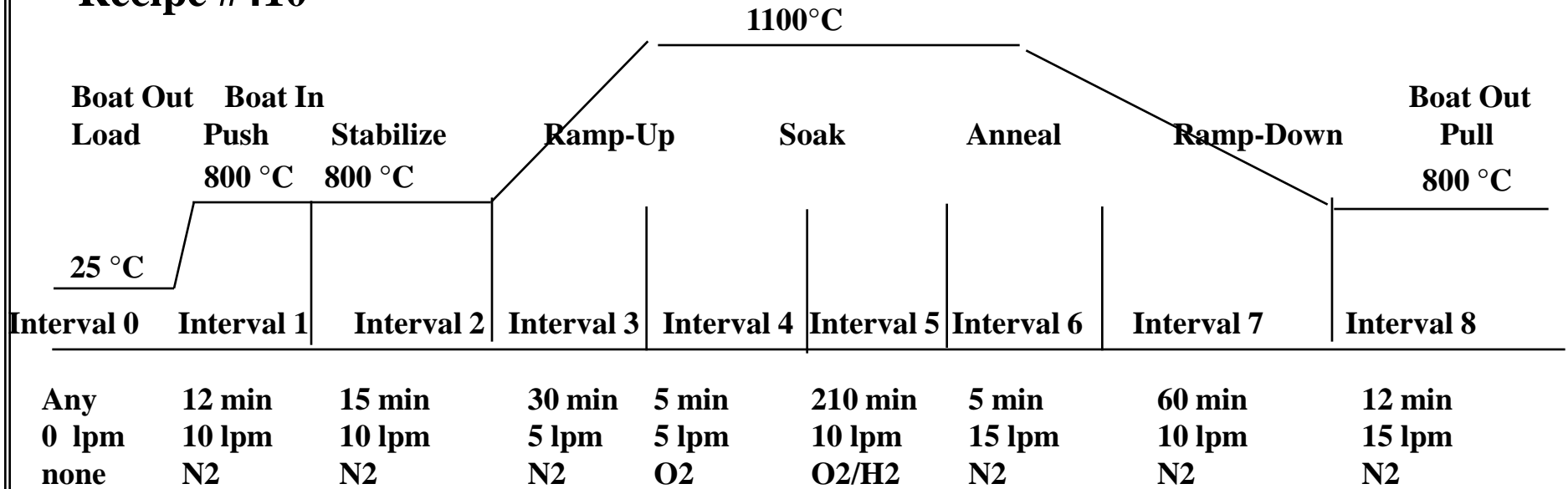
Wet Oxide Growth, Target 6,500 Å

Rochester Institute of Technology
Microelectronic Engineering



BRUCE FURNACE RECIPE 410 – WET OXIDE 12,000Å

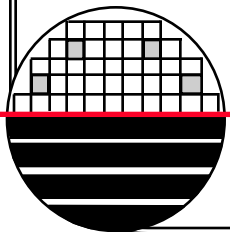
Recipe #410



At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

Wet Oxide Growth, Target 12,000 Å

Rochester Institute of Technology
Microelectronic Engineering



BRUCE FURNACE RECIPE 430 – WET OXIDE 30,000Å

Recipe #430

1100°C

Boat Out Load

Boat In Push

Stabilize

Ramp-Up

Soak

Anneal

Ramp-Down

Boat Out Pull

800 °C

800 °C

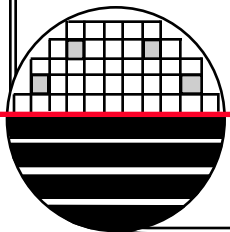
25 °C

Interval 0	Interval 1	Interval 2	Interval 3	Interval 4	Interval 5	Interval 6	Interval 7	Interval 8
Any	12 min	15 min	30 min	5 min	15 hrs	5 min	60 min	12 min
0 lpm	10 lpm	10 lpm	5 lpm	5 lpm	10 lpm	15 lpm	10 lpm	15 lpm
none	N2	N2	N2	O2	O2/H2	N2	N2	N2

At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

Wet Oxide Growth, Target 30,000 Å

Rochester Institute of Technology
Microelectronic Engineering



BRUCE FURNACE RECIPE 440 – WET OXIDE 40,000Å

Recipe #440

1100°C

Boat Out Load
Boat In Push
800 °C

Stabilize
800 °C

Ramp-Up

Soak

Anneal

Ramp-Down

Boat Out Pull
800 °C

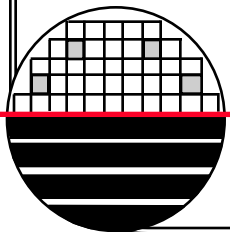
25 °C

Interval 0	Interval 1	Interval 2	Interval 3	Interval 4	Interval 5	Interval 6	Interval 7	Interval 8
Any	12 min	15 min	30 min	5 min	35 hrs	5 min	60 min	12 min
0 lpm	10 lpm	10 lpm	5 lpm	10 lpm	3.6/2.0 lpm	15 lpm	10 lpm	5 lpm
none	N2	N2	N2	O2	O2/H2	N2	N2	N2

At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

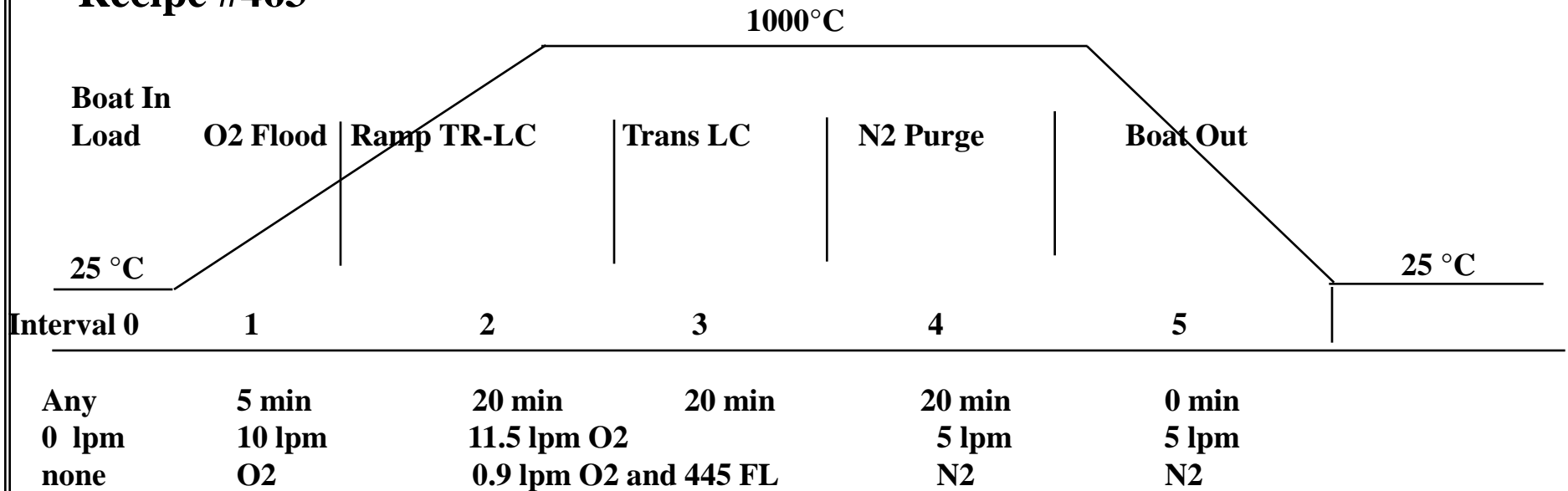
Wet Oxide Growth, Target 40,000 Å

Rochester Institute of Technology
Microelectronic Engineering



BRUCE FURNACE RECIPE 463 – TransLC CLEAN

Recipe #463



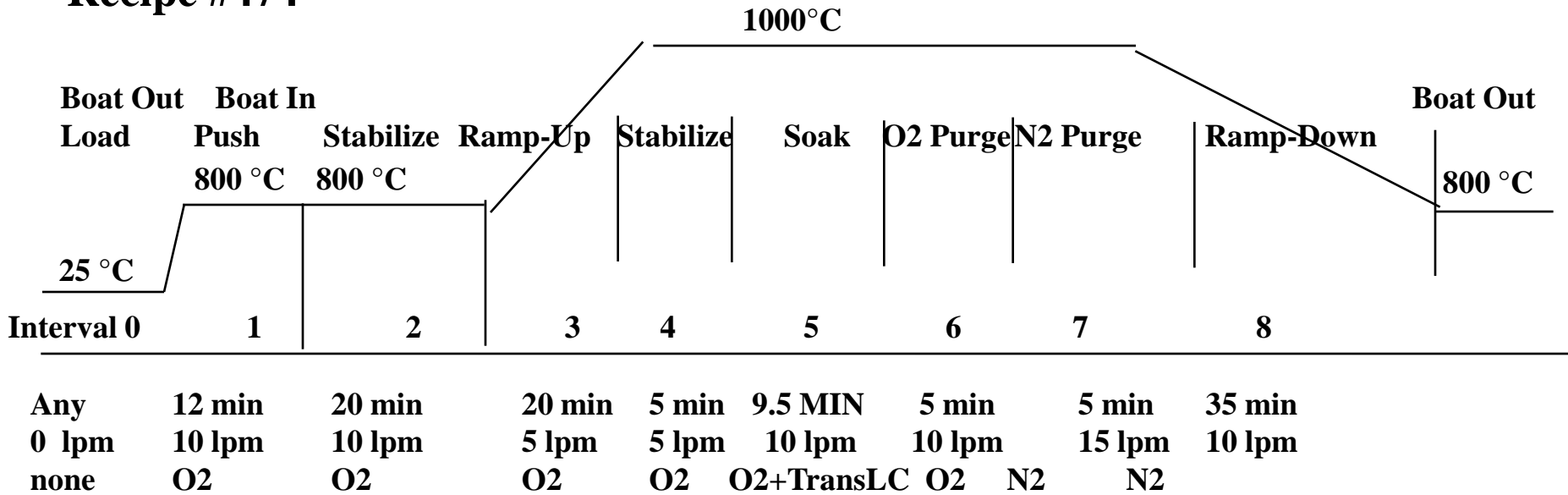
At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

1000 °C Trans LC Tube Clean, Tube 4

Rochester Institute of Technology
Microelectronic Engineering

BRUCE FURNACE RECIPE 474 – GATE OXIDE 310Å

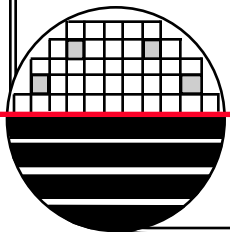
Recipe #474



At the end of a run the furnace returns to Interval 0 which is set for boat out, 25 °C and no gas flow. The furnace waits in that state until someone aborts the current recipe or loads a new recipe.

1000°C 310Å Gate Oxide Growth

Rochester Institute of Technology
Microelectronic Engineering



REFERENCES

1. Sdfklj
2. slfj